

Fig. 1

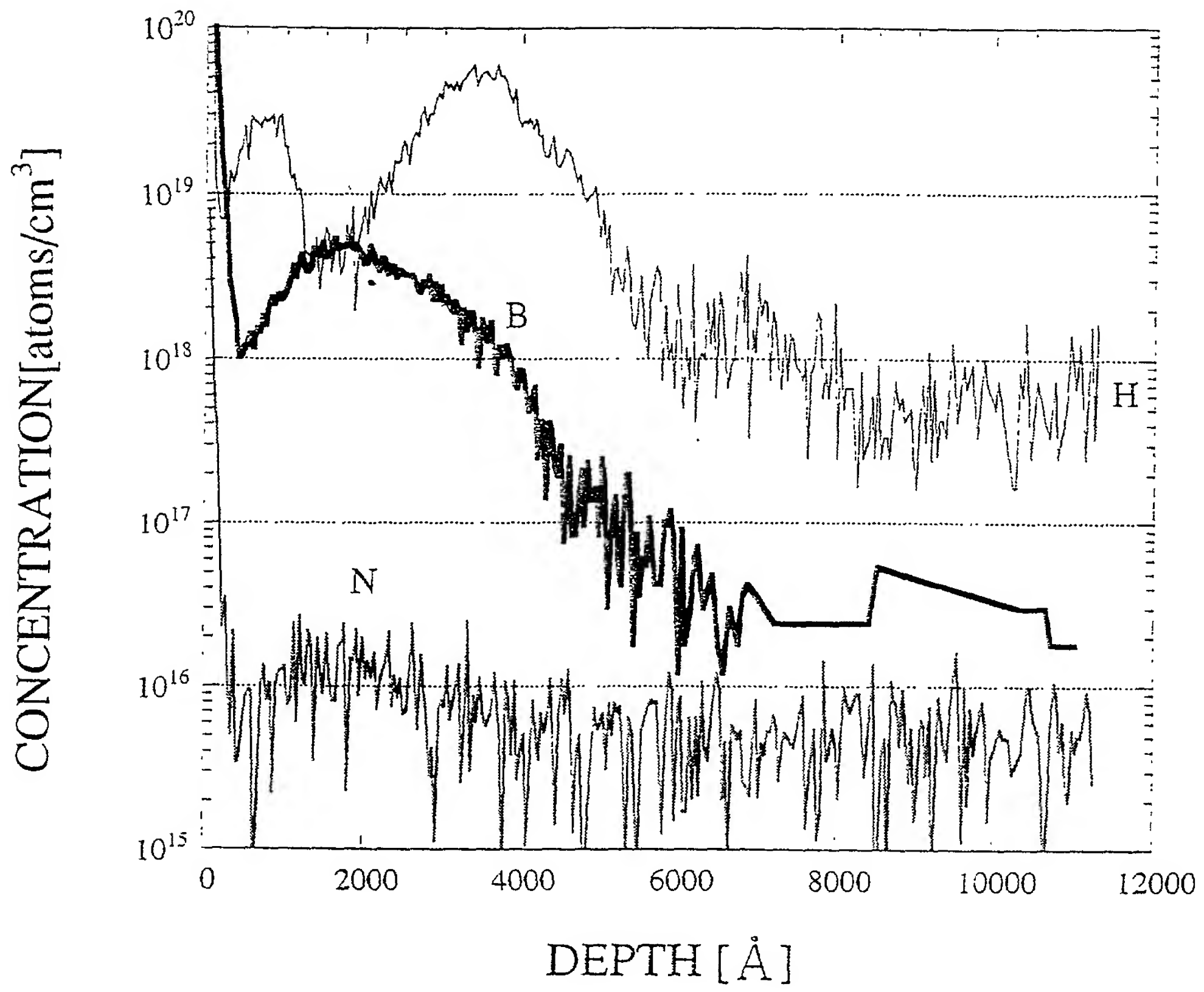


Fig. 2

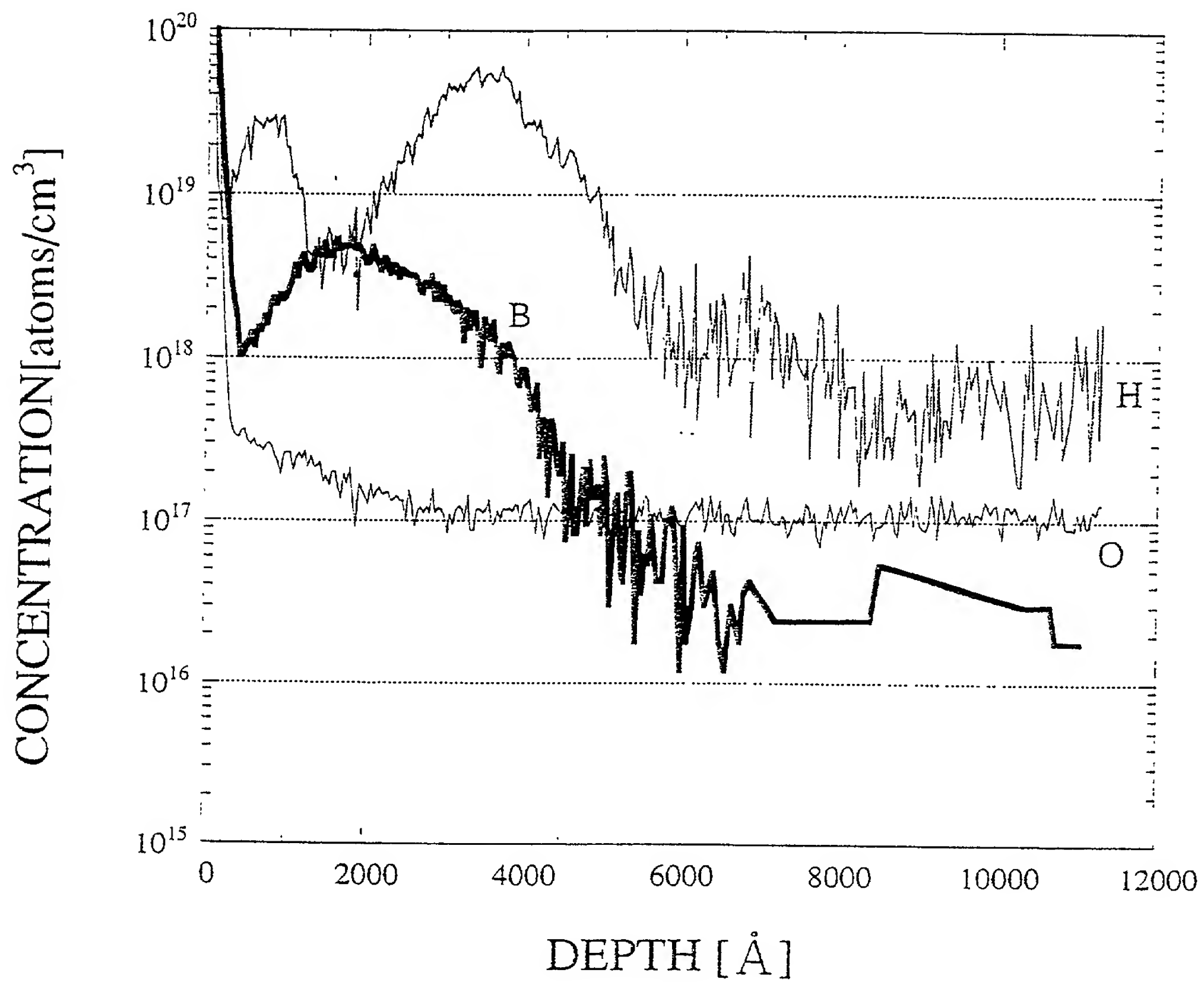


Fig. 3

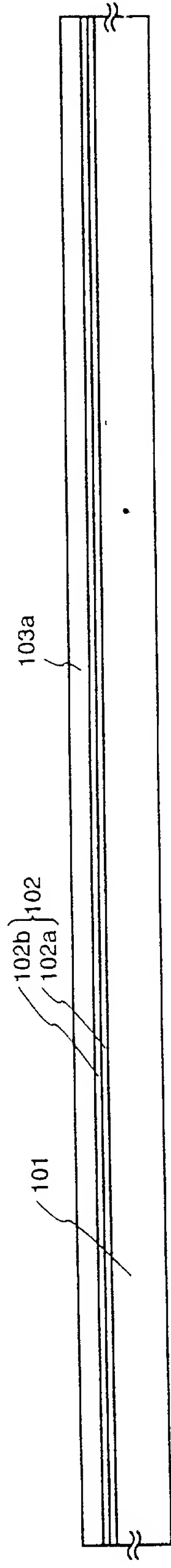


Fig. 4A

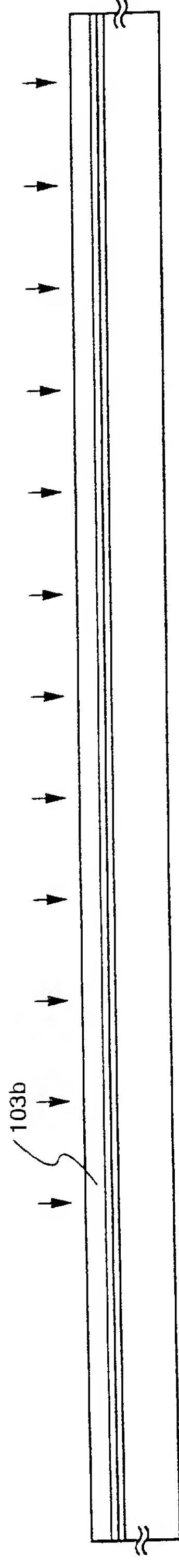


Fig. 4B

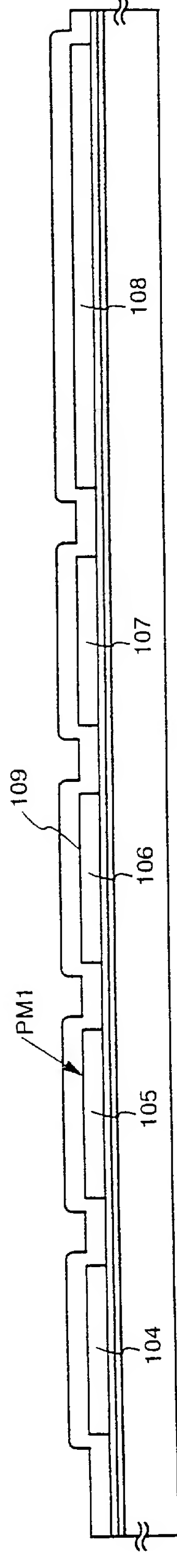


Fig. 4C

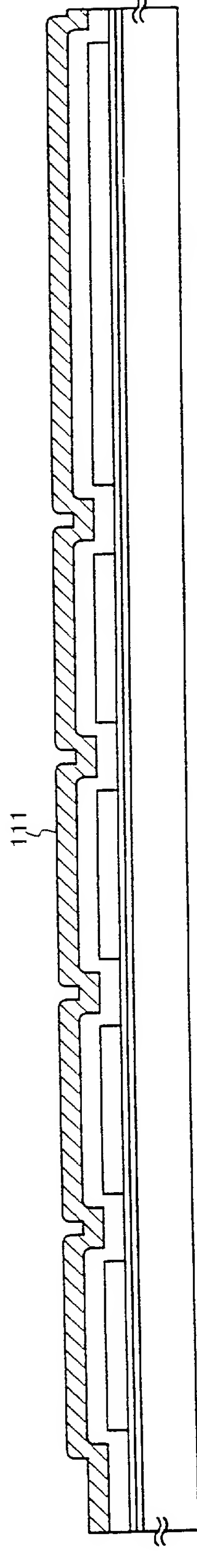


Fig. 4D

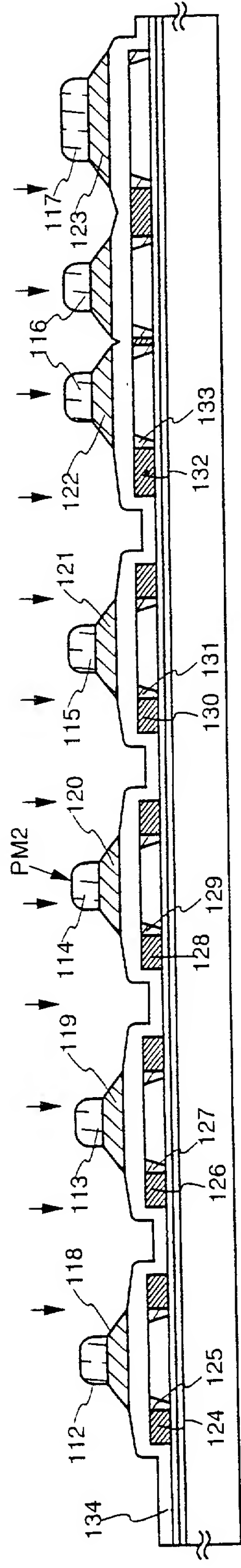


Fig. 5A

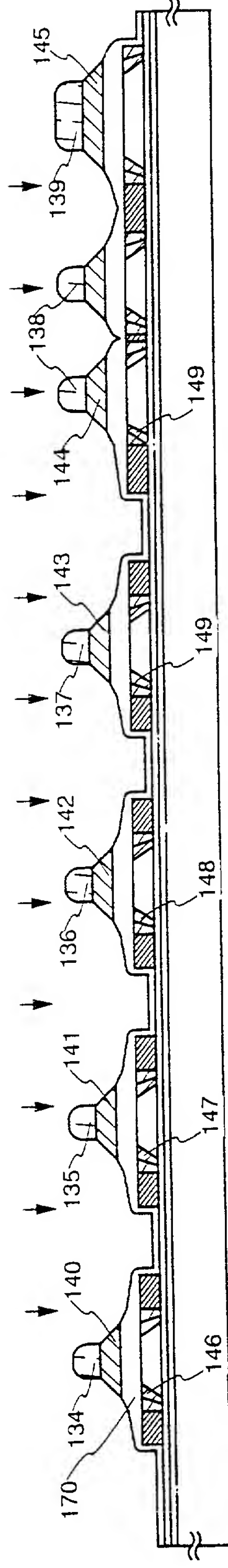


Fig. 5B

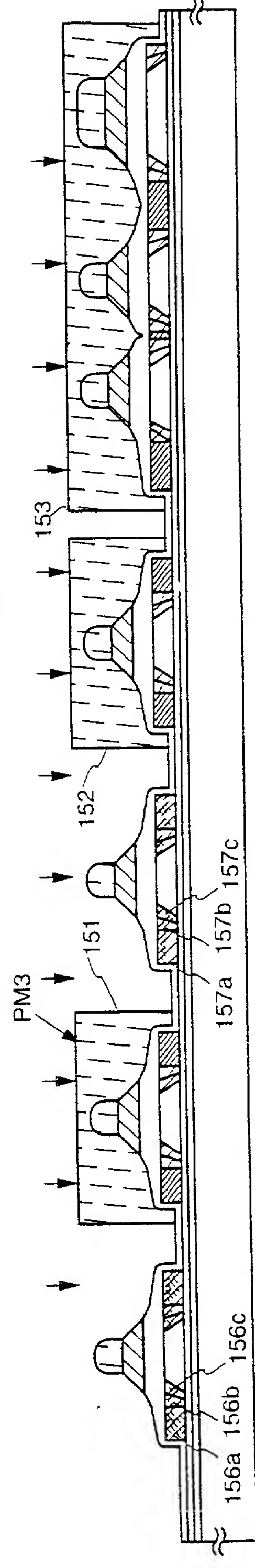


Fig. 5C

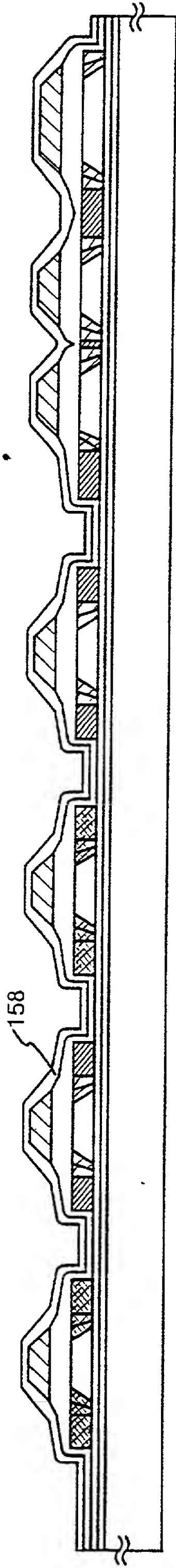


Fig. 6A

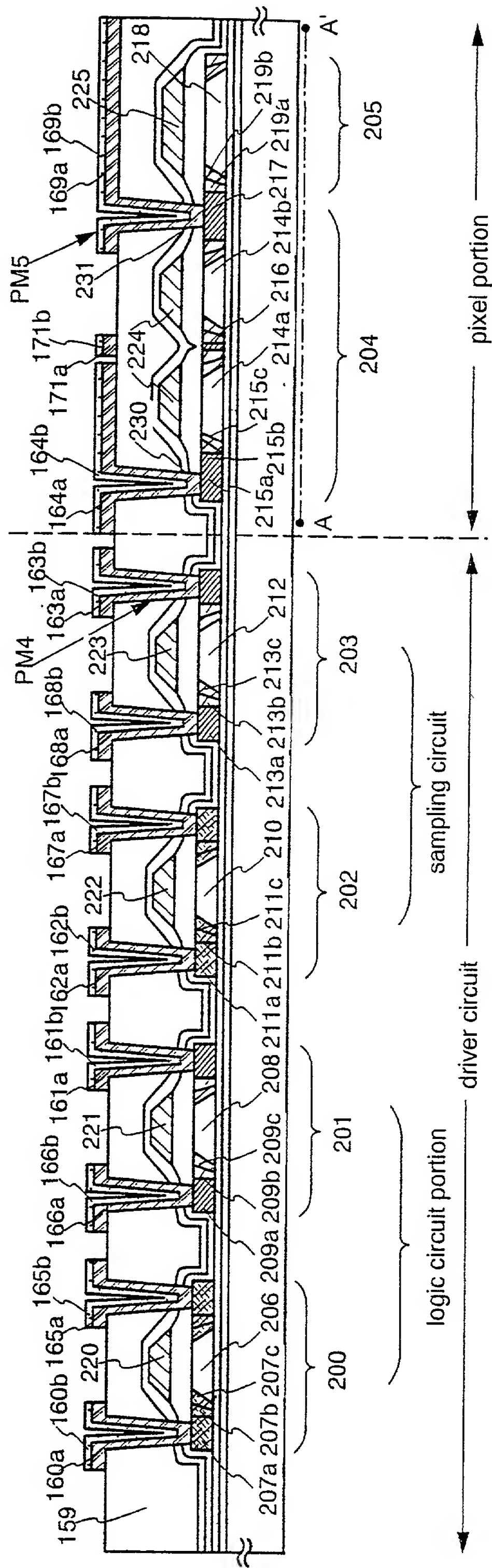


Fig. 6B

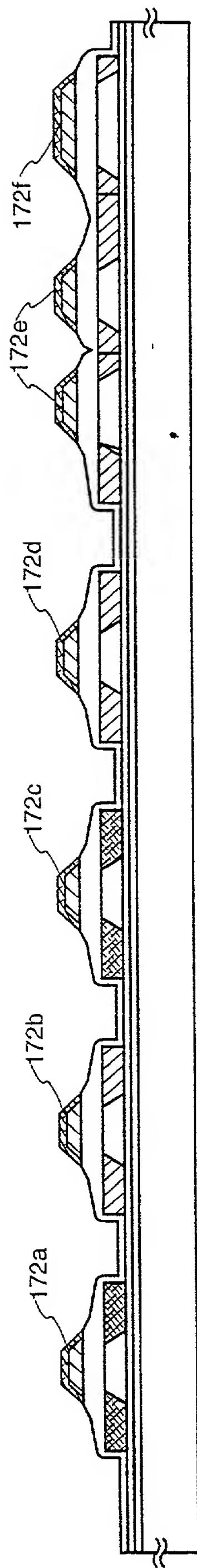


Fig. 7A

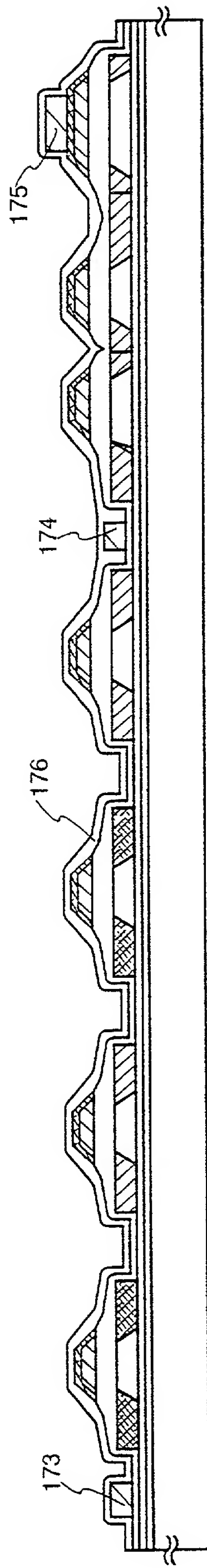


Fig. 7B

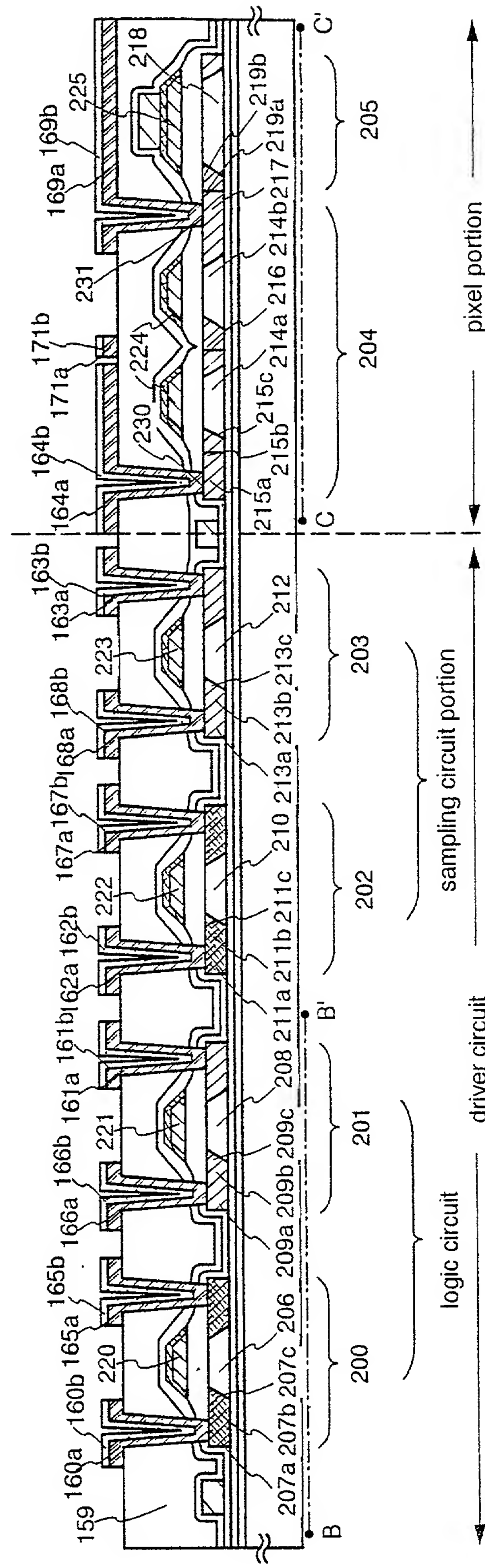


Fig. 8A

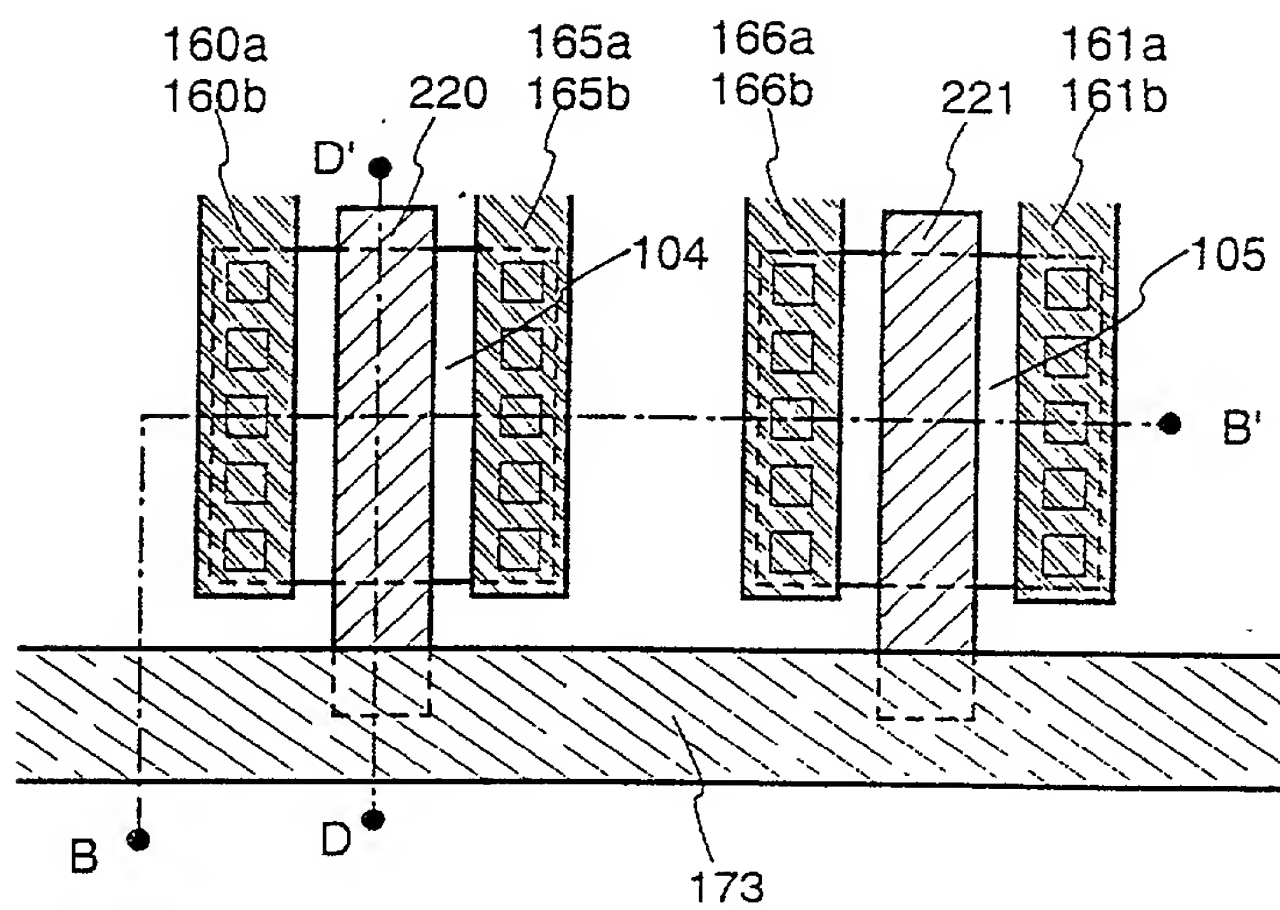


Fig. 8B

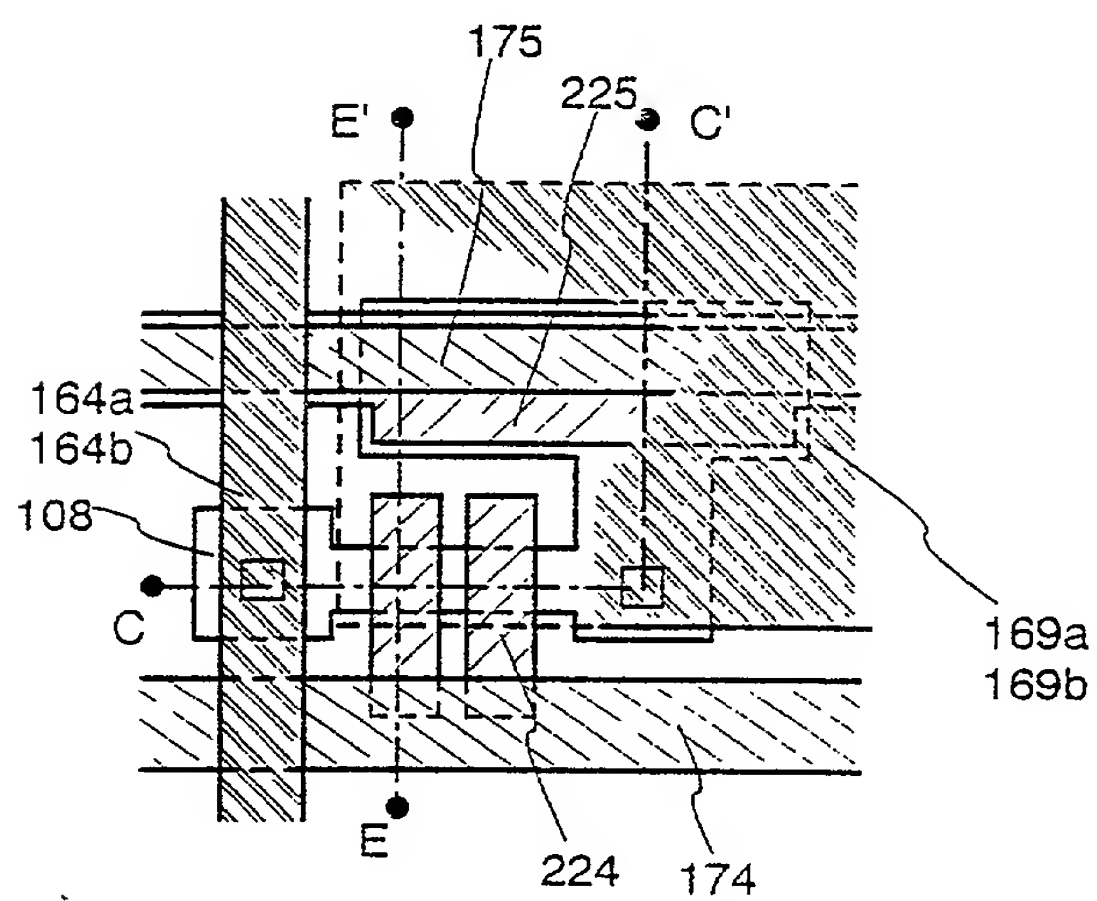


Fig. 9A

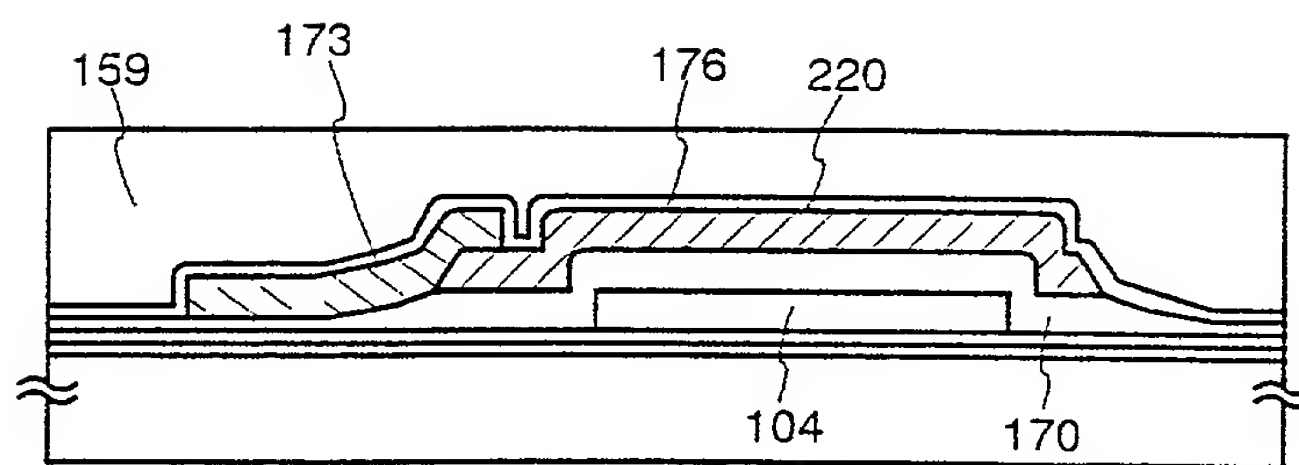


Fig. 9B

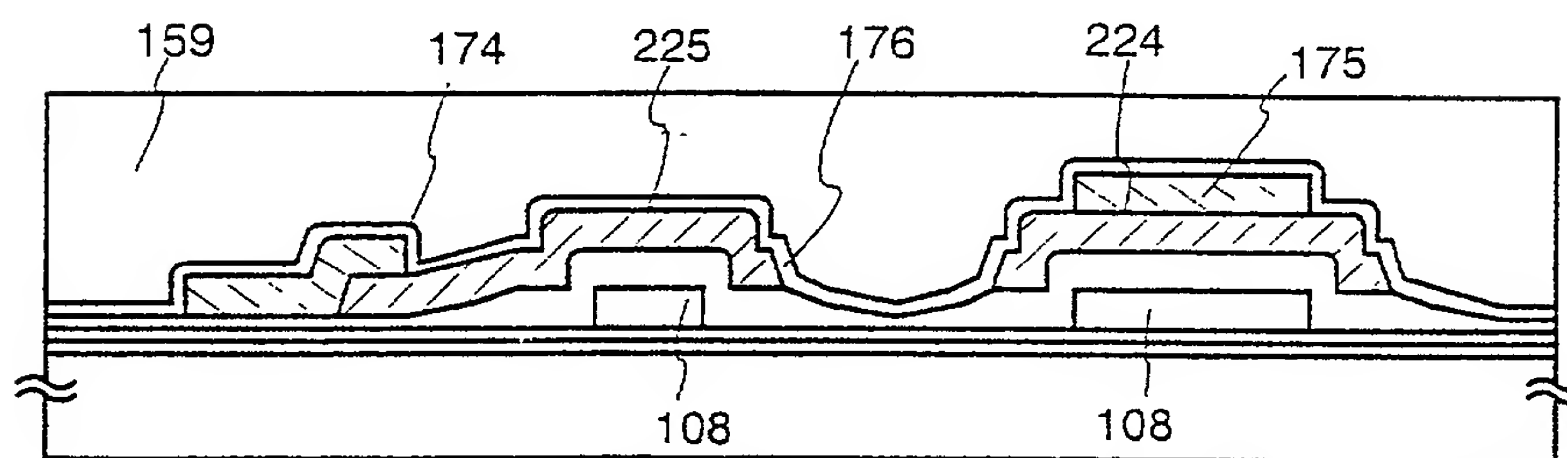


Fig. 10A

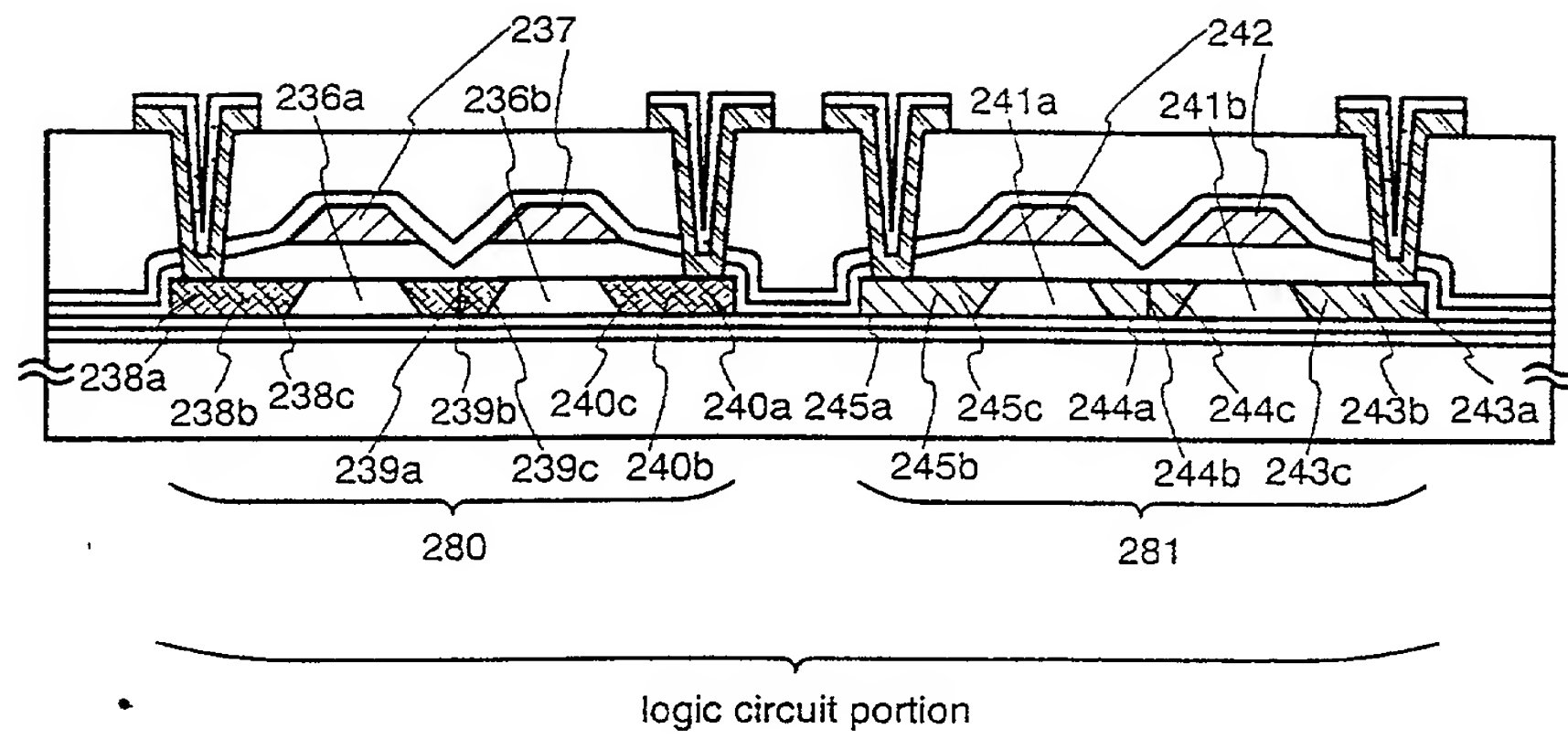


Fig. 10B

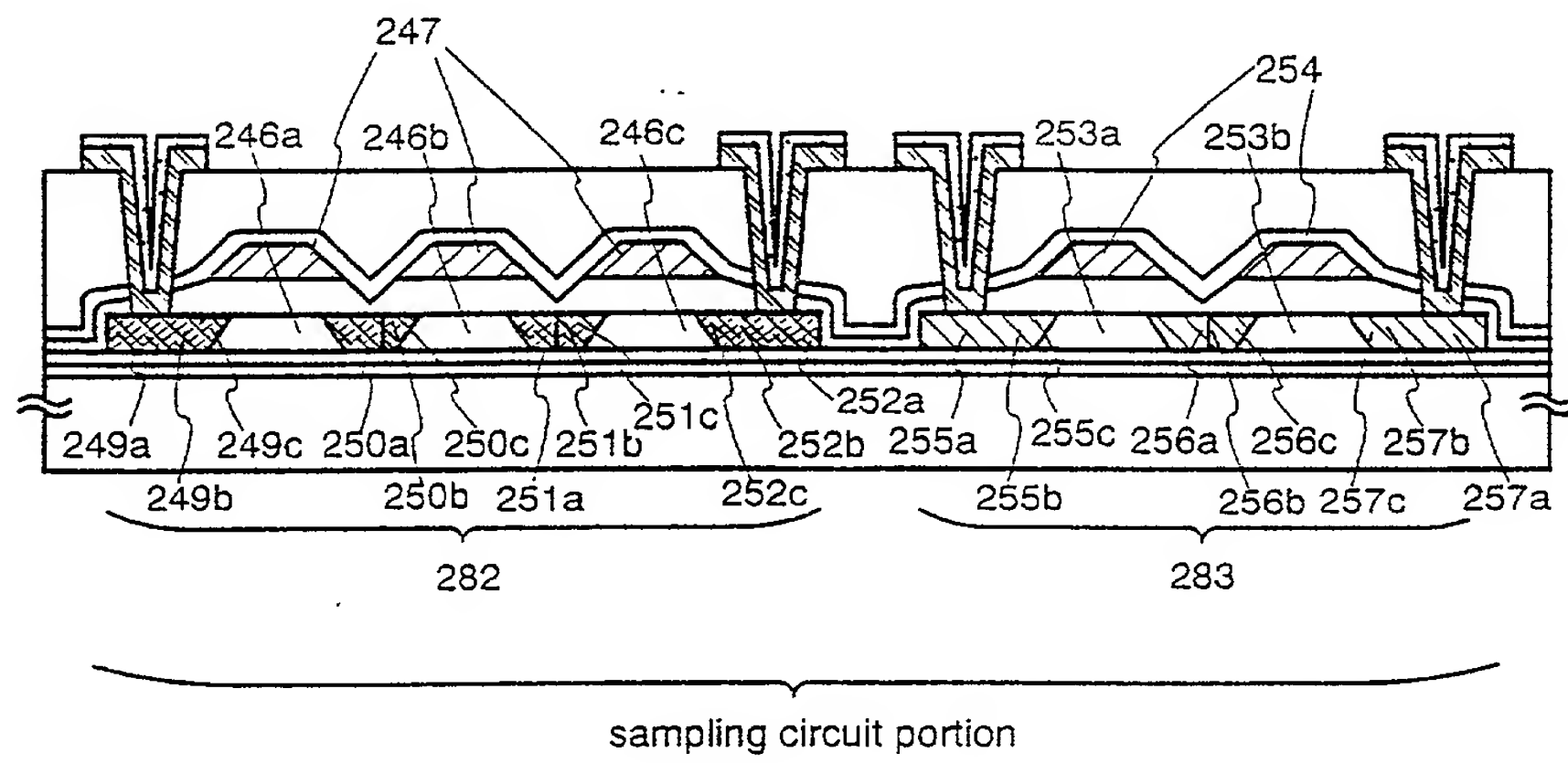


Fig. 11A

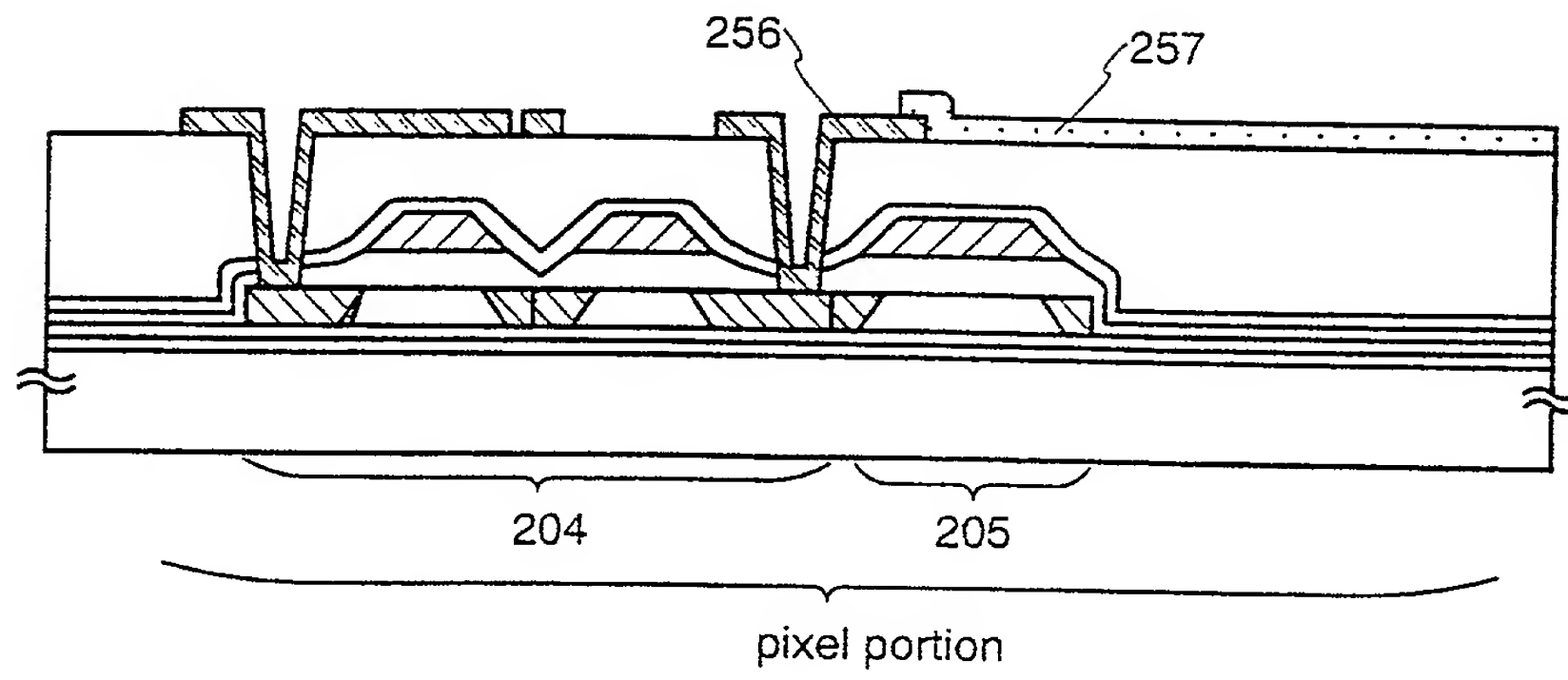


Fig. 11B

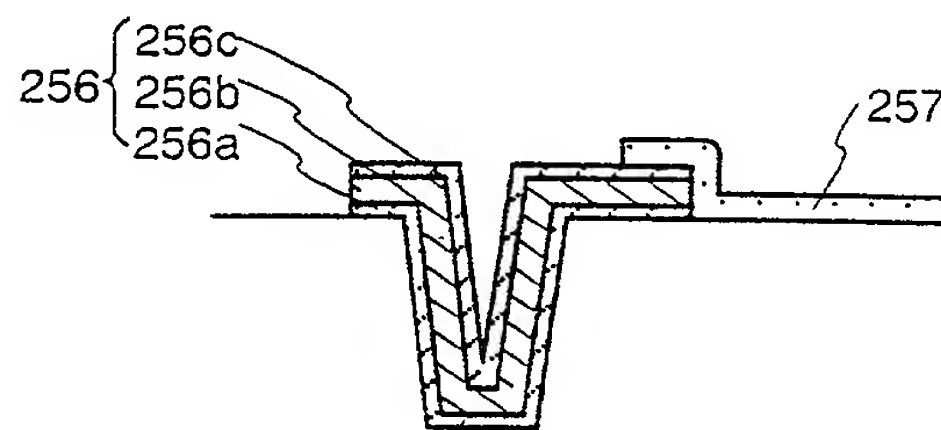


Fig. 11C

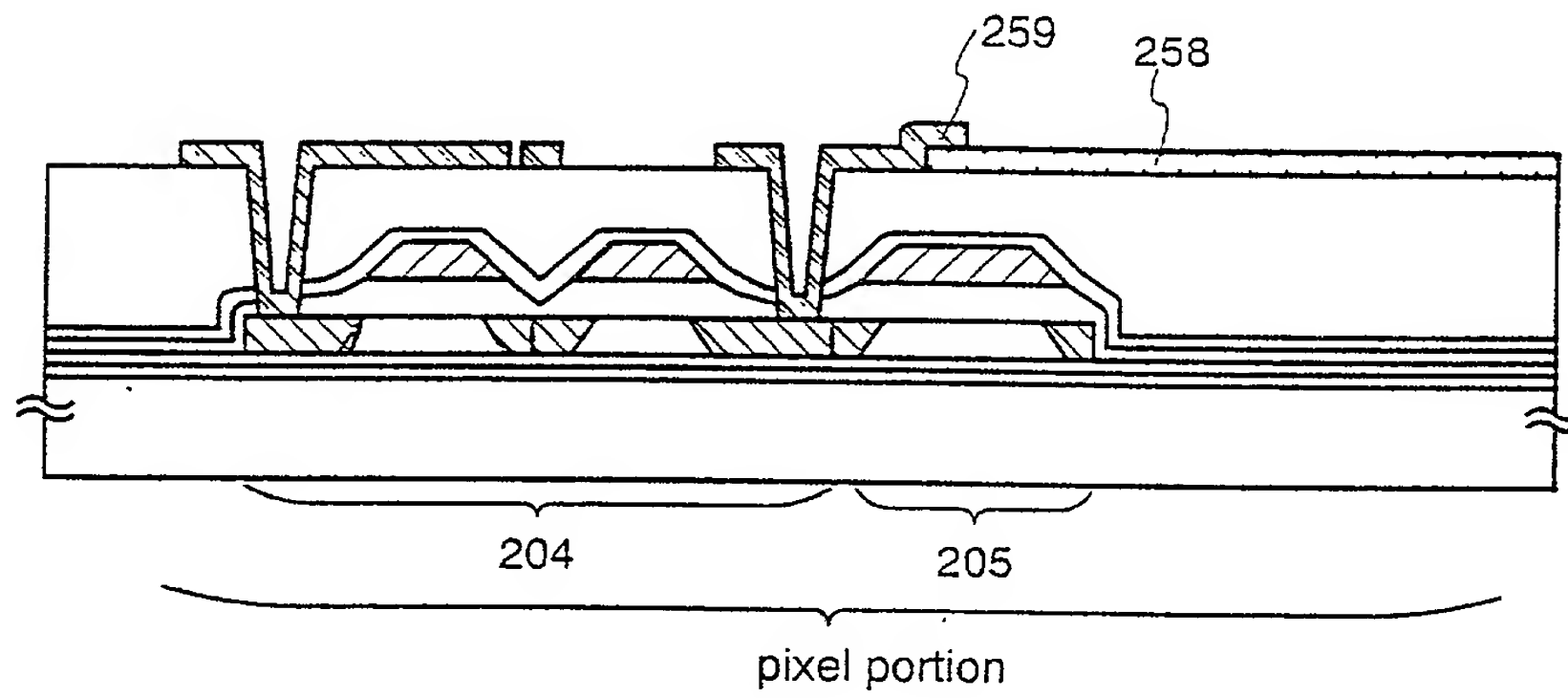
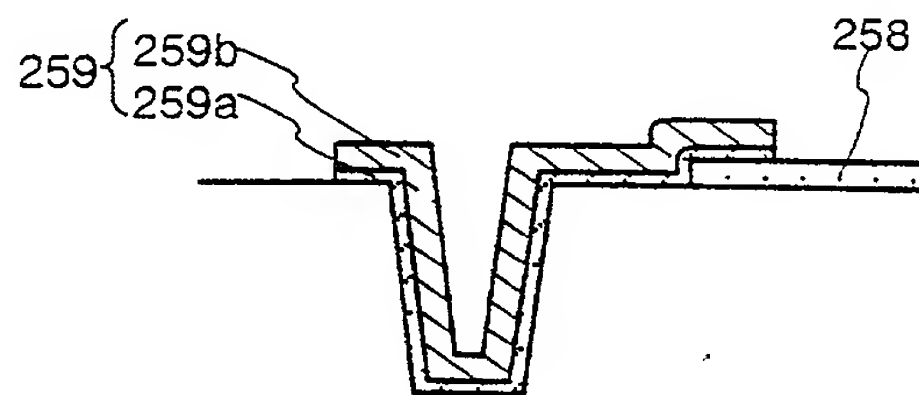


Fig. 11D



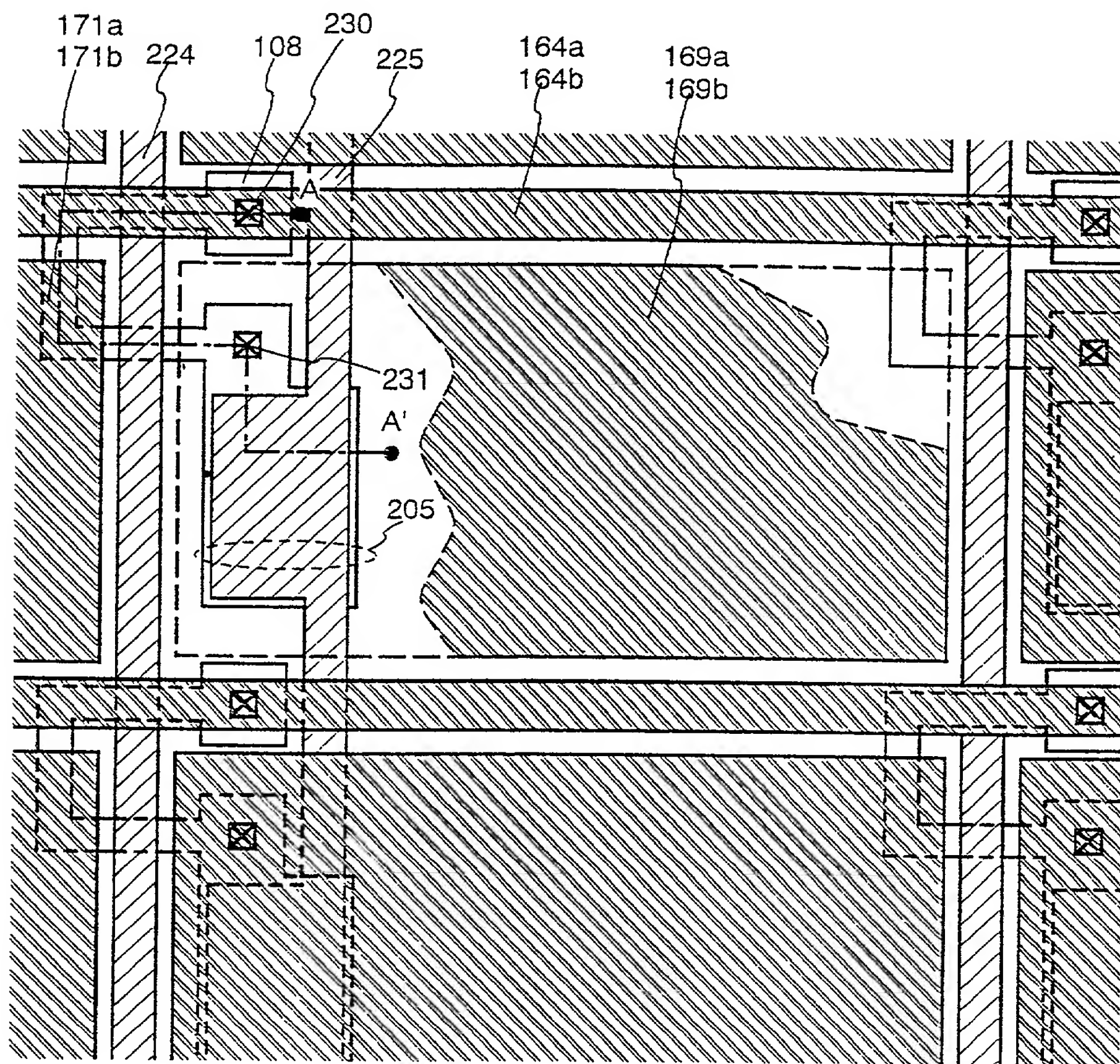
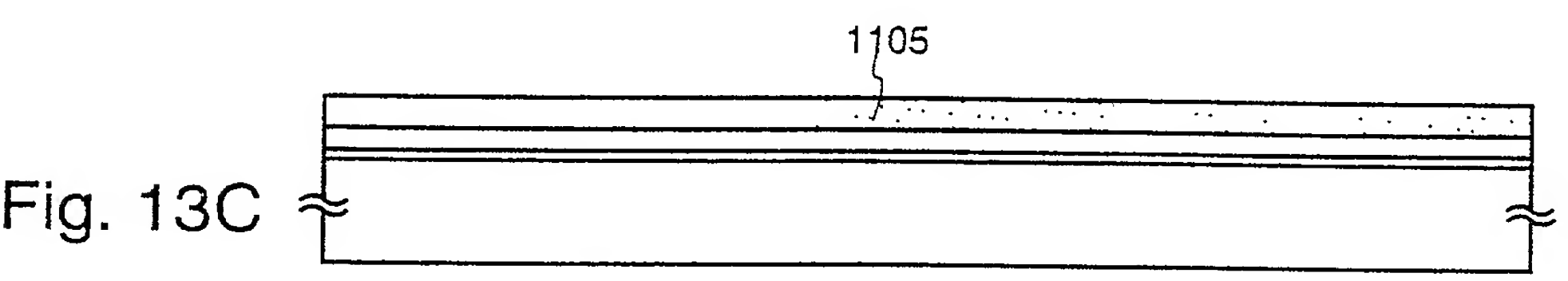
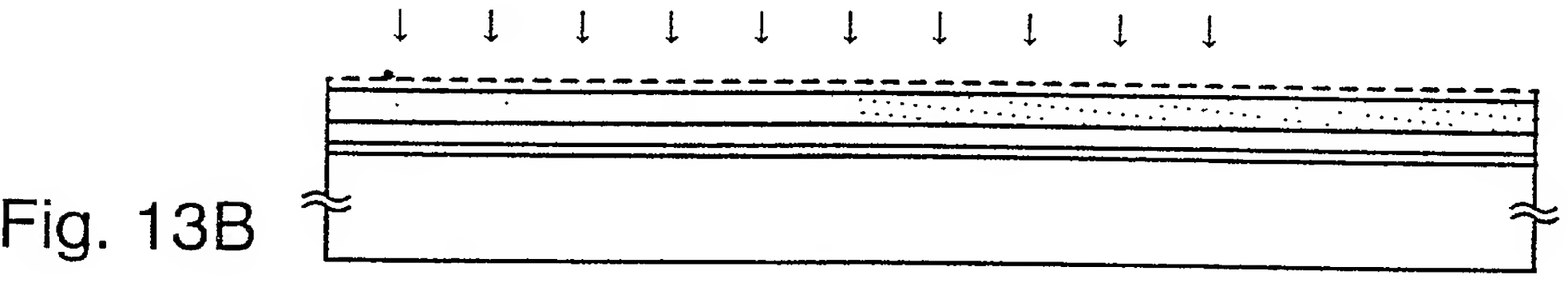
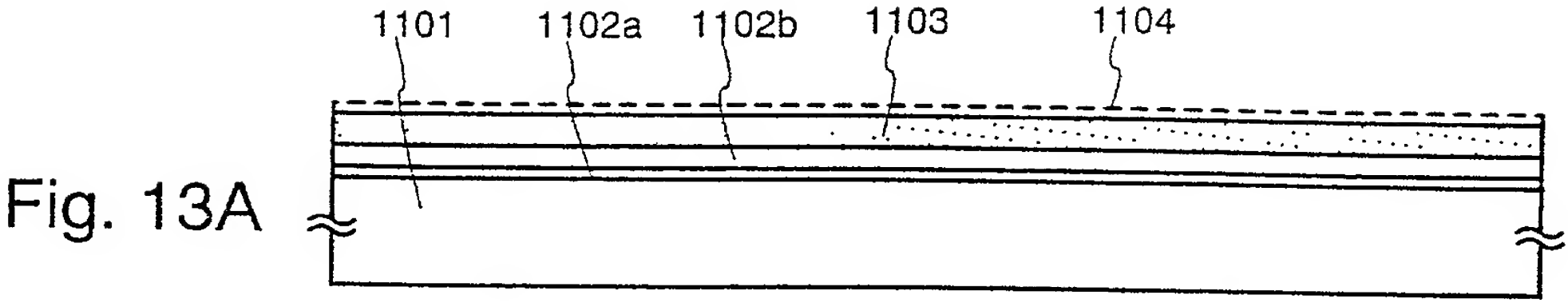


Fig. 12



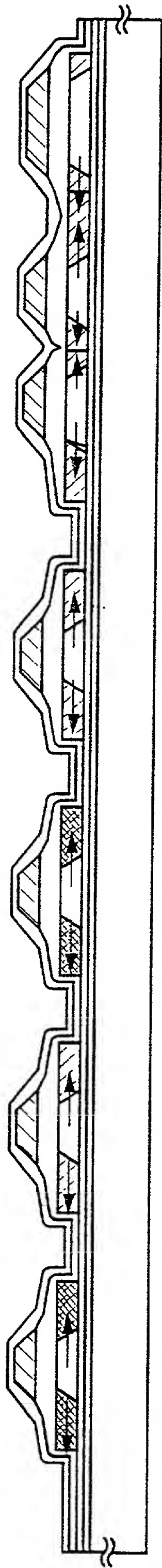


Fig. 14

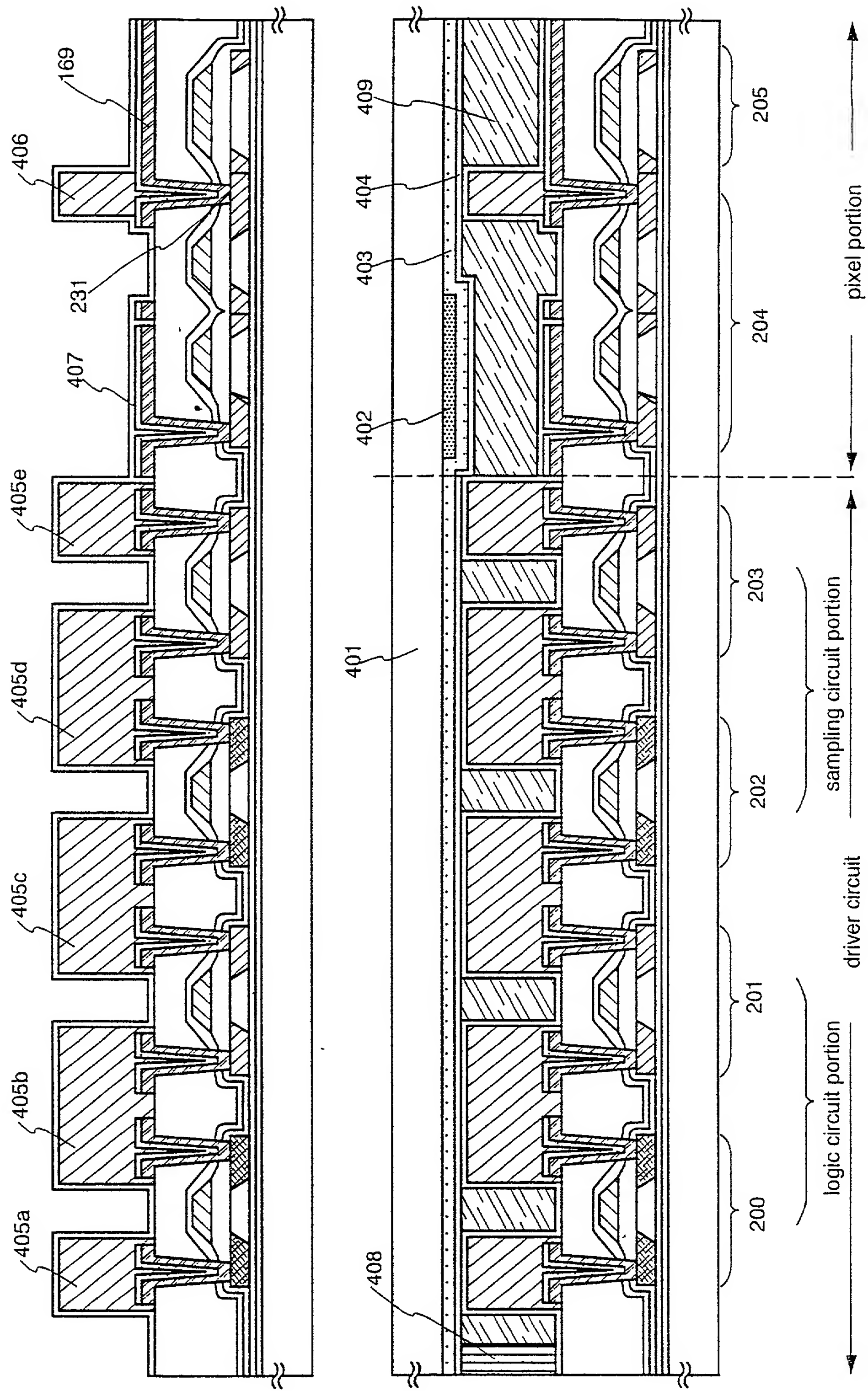


Fig. 15

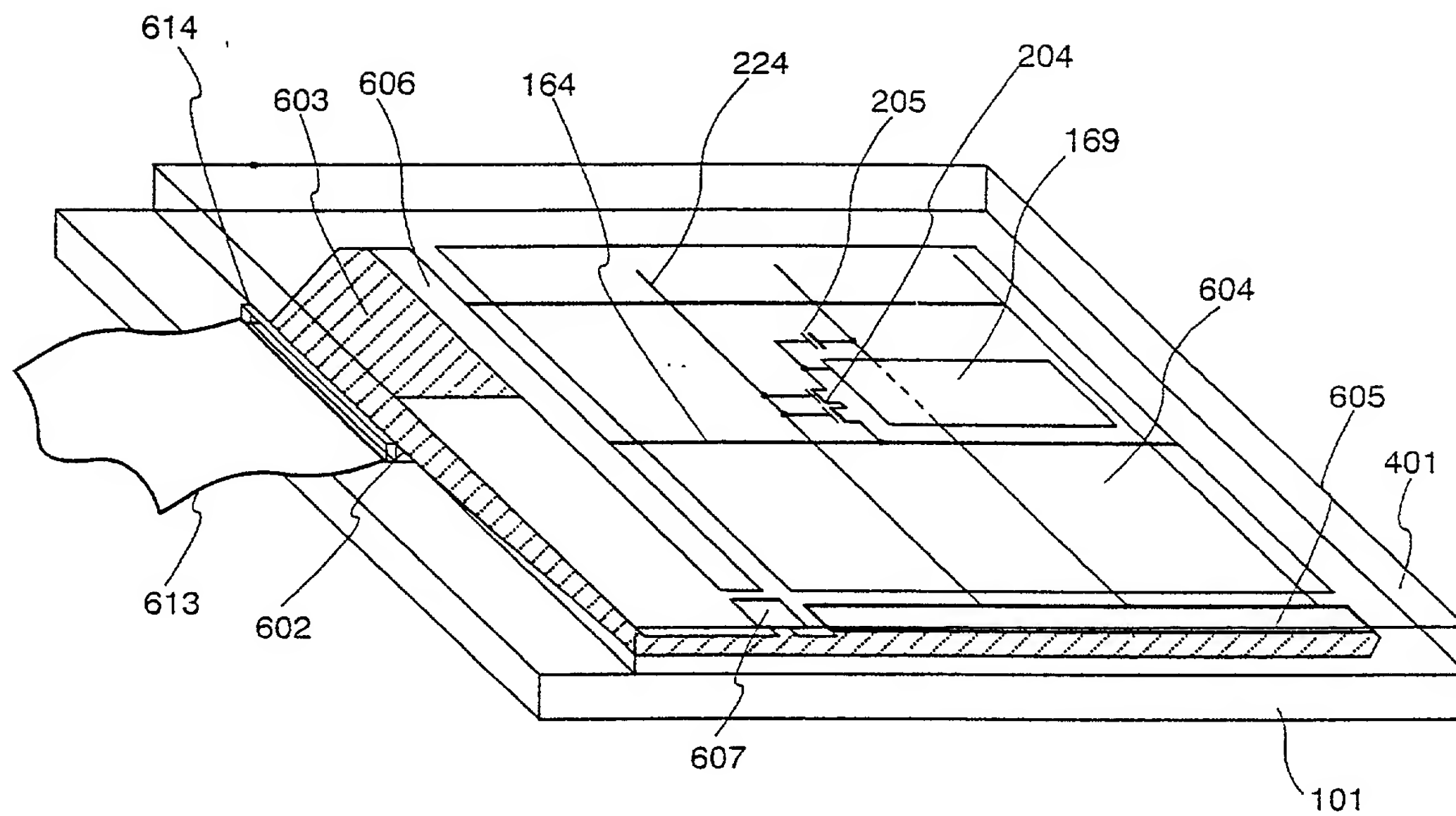


Fig. 16

Fig. 17A

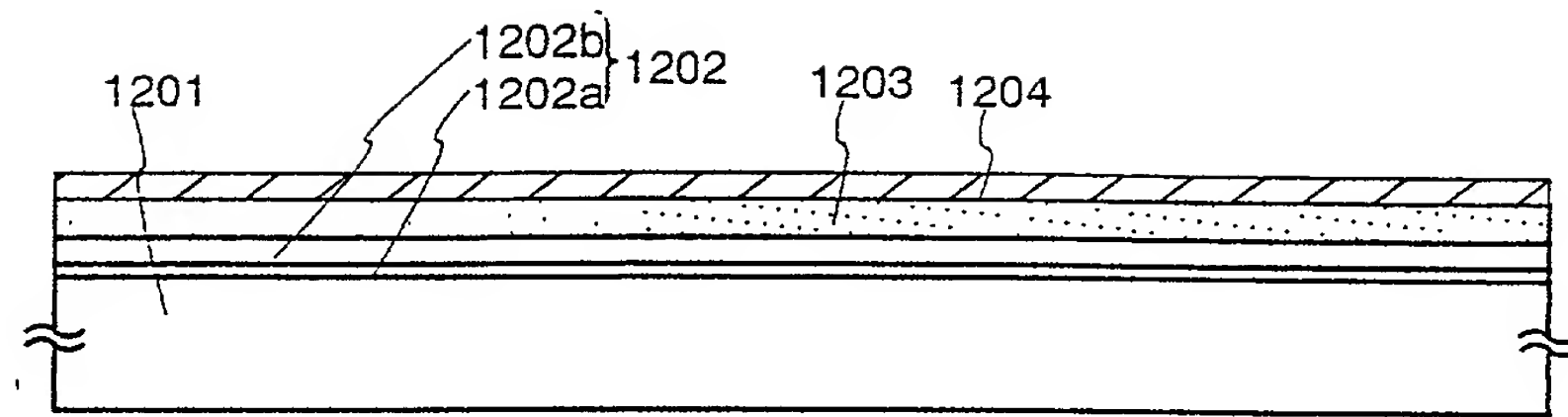


Fig. 17B

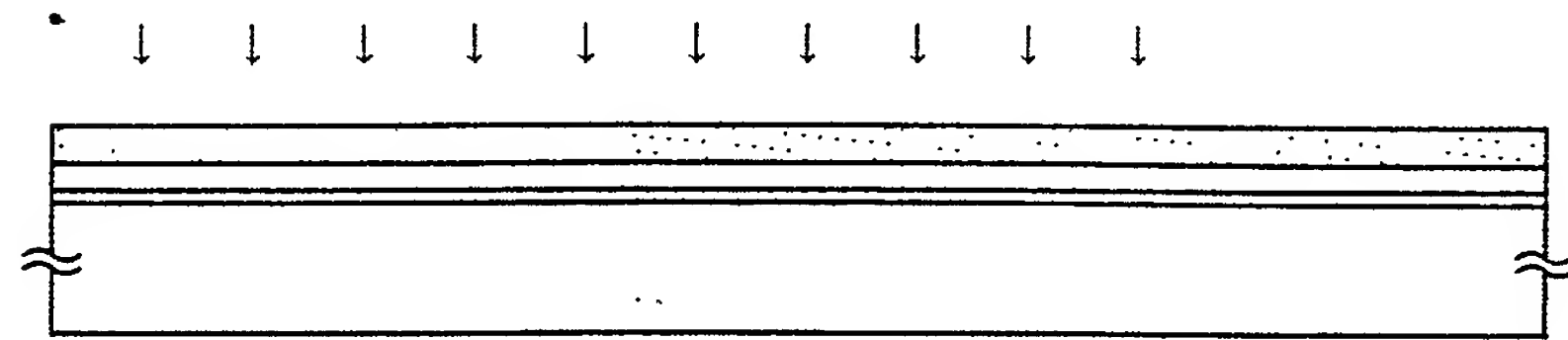
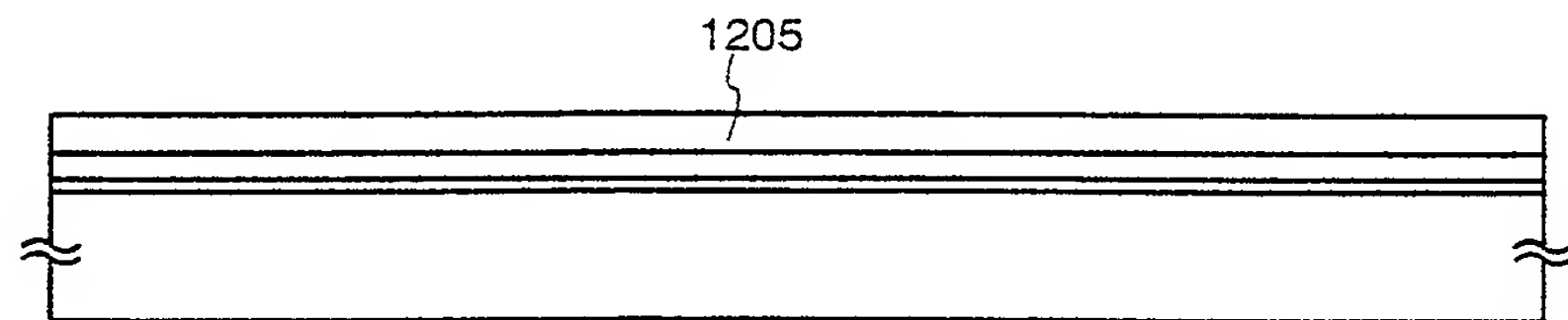


Fig. 17C



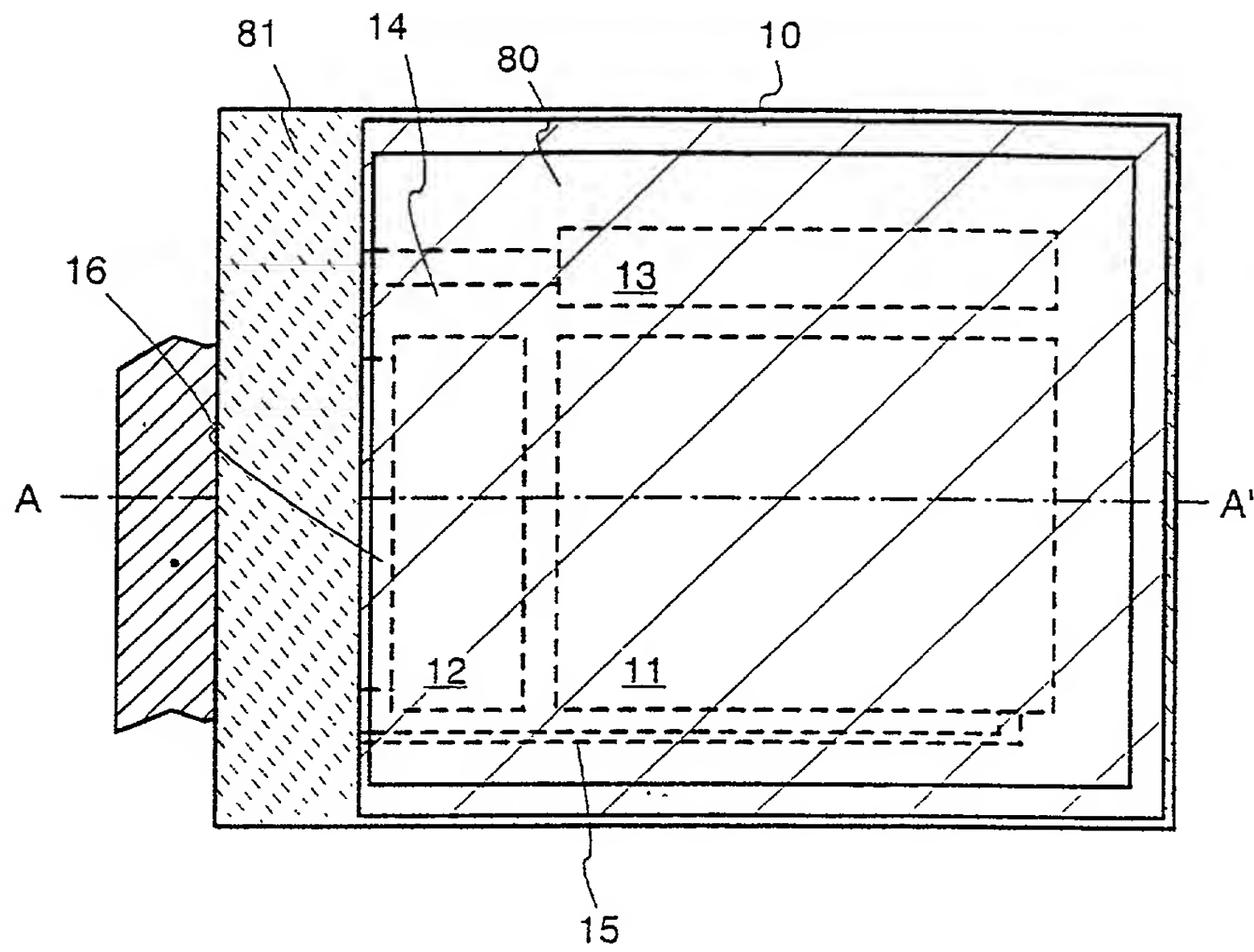


Fig. 18A

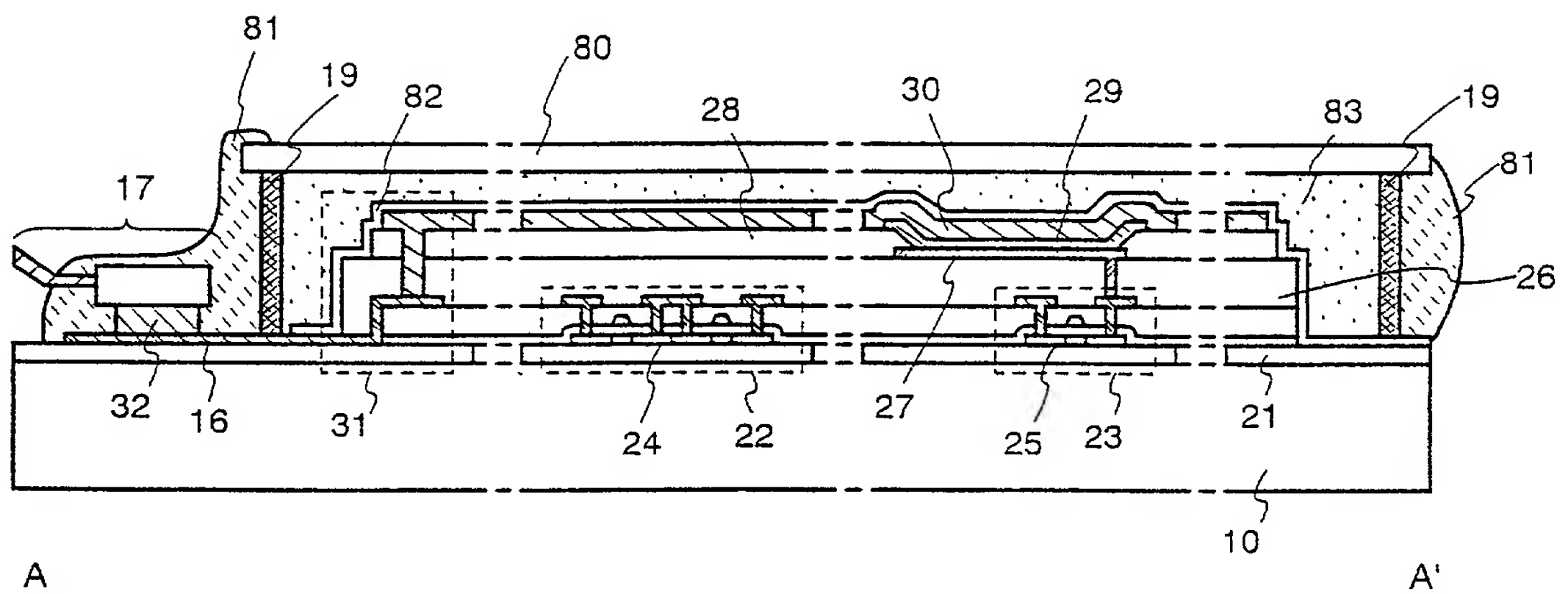
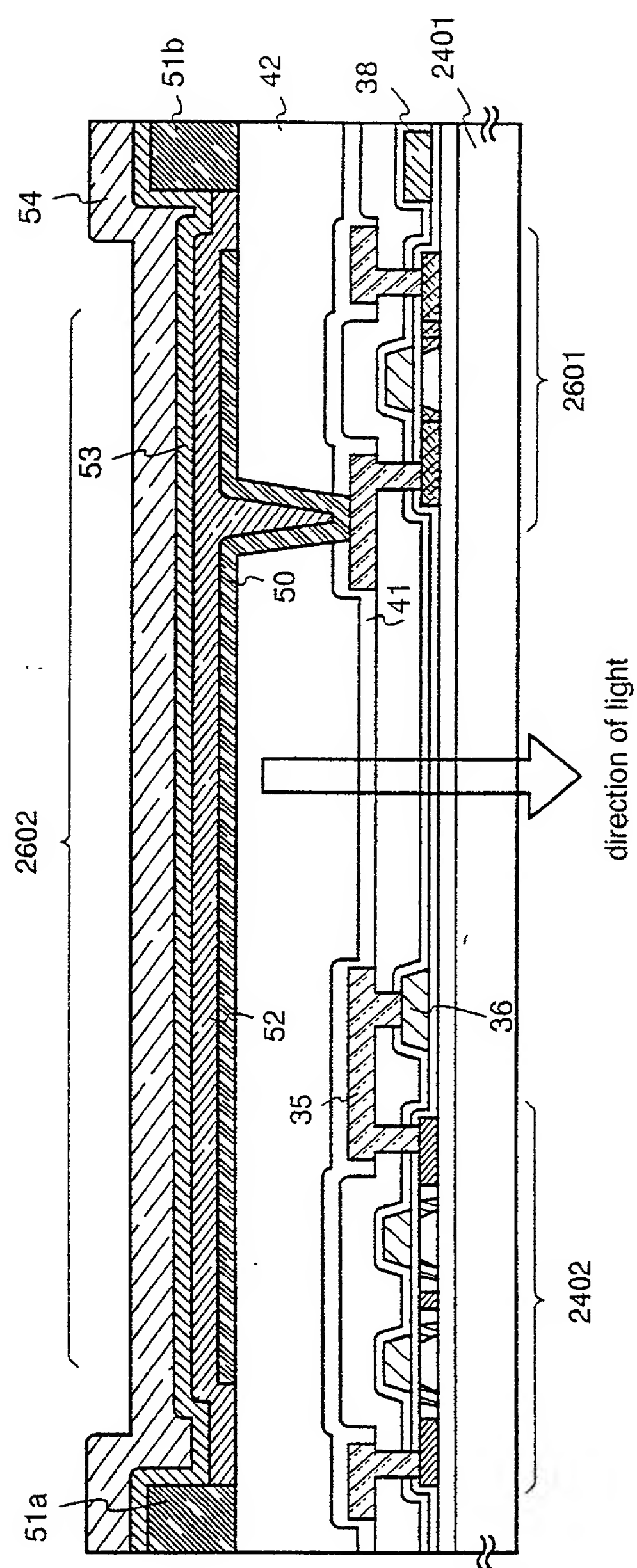
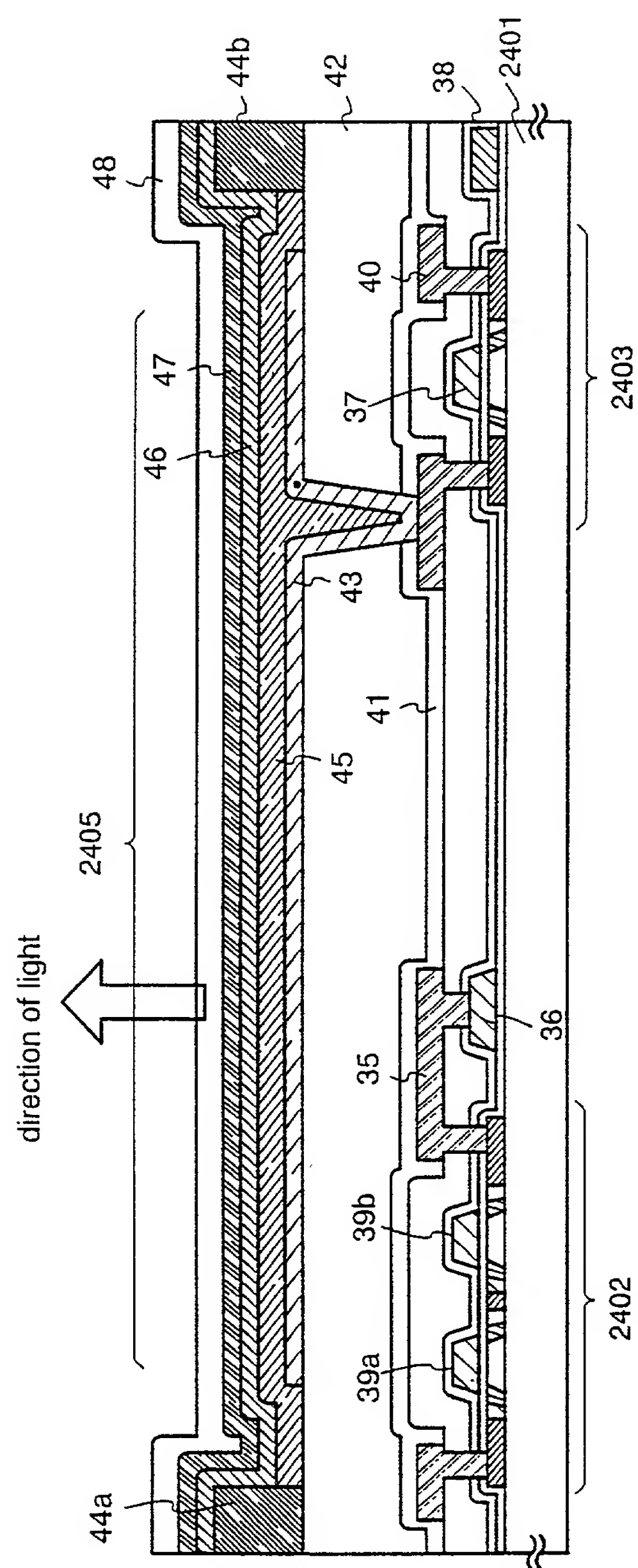


Fig. 18B



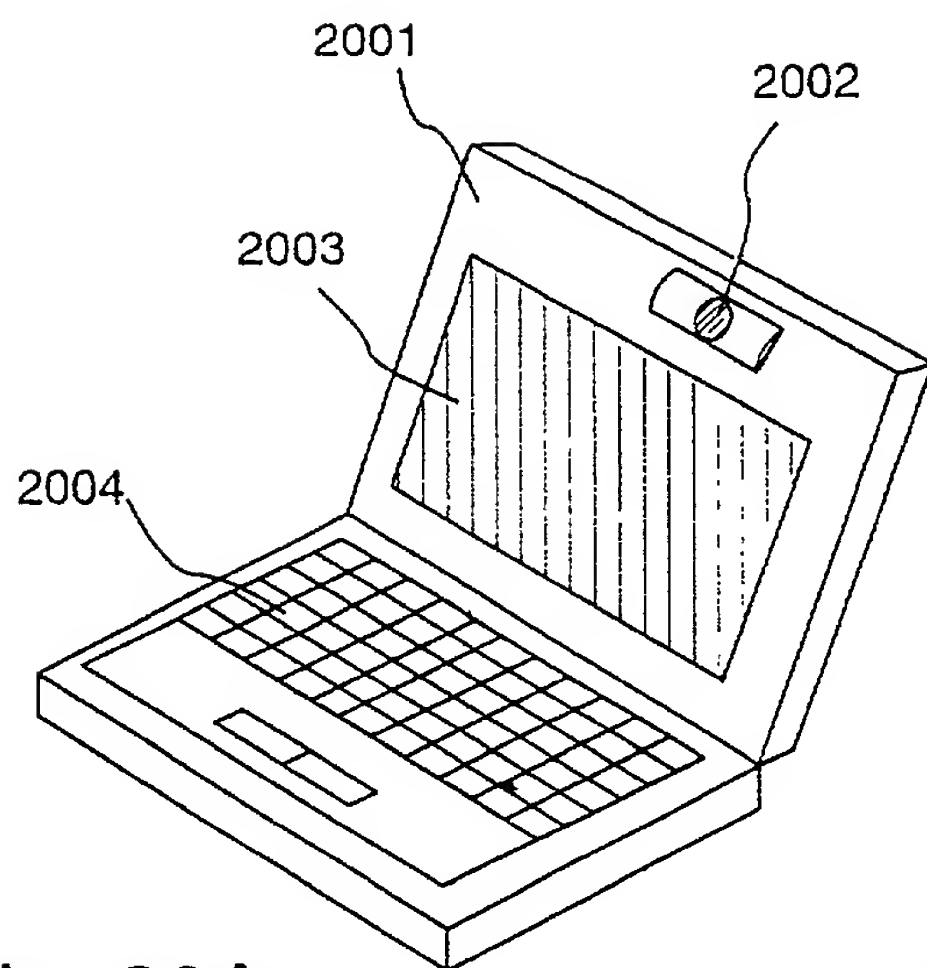


Fig. 20A

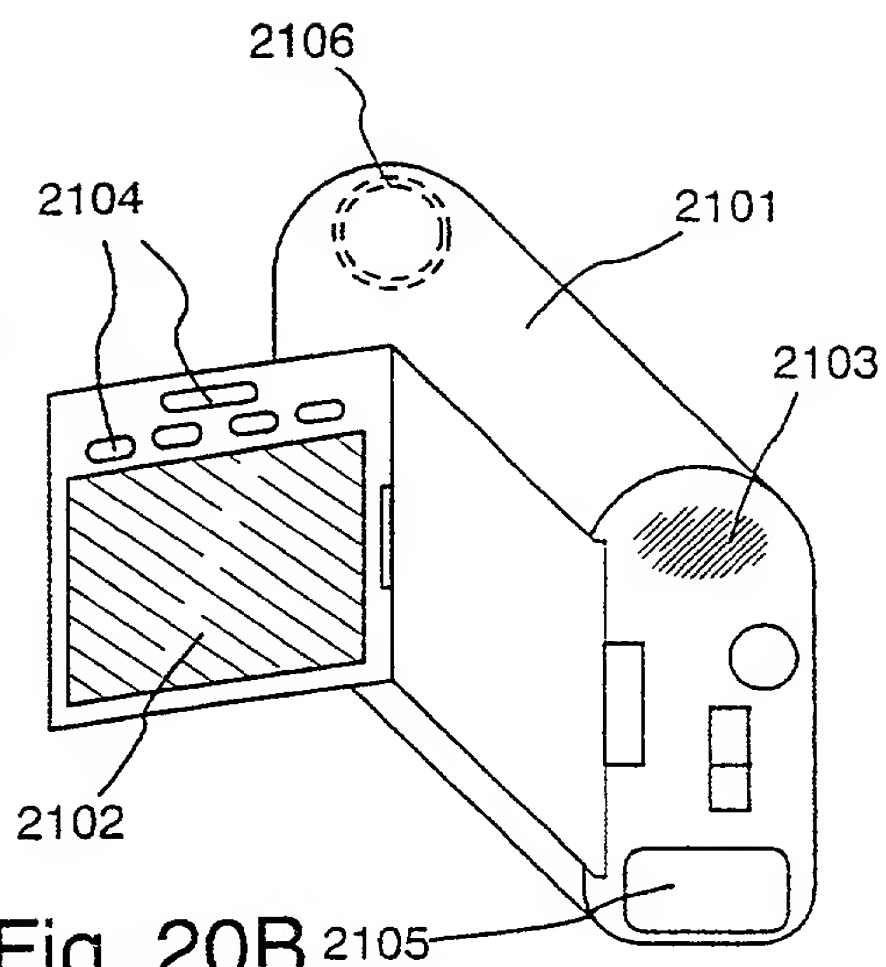


Fig. 20B

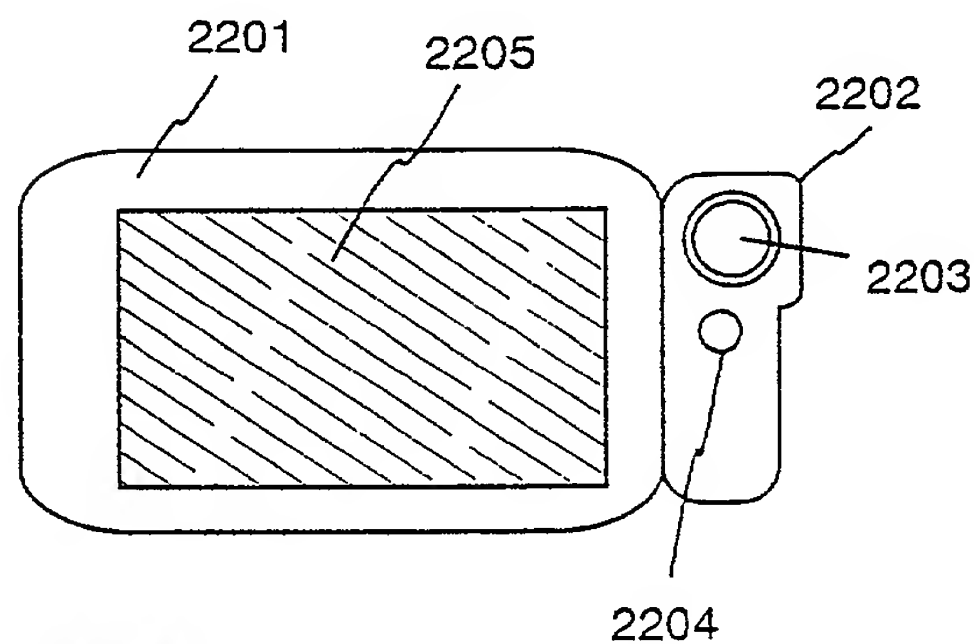


Fig. 20C

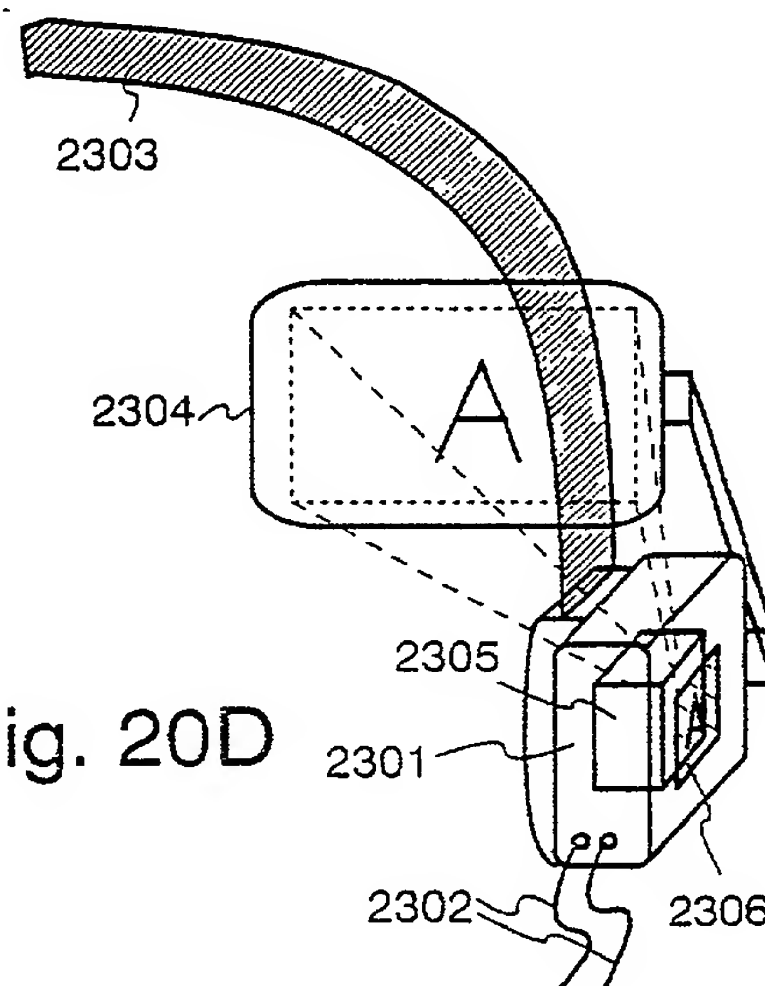


Fig. 20D

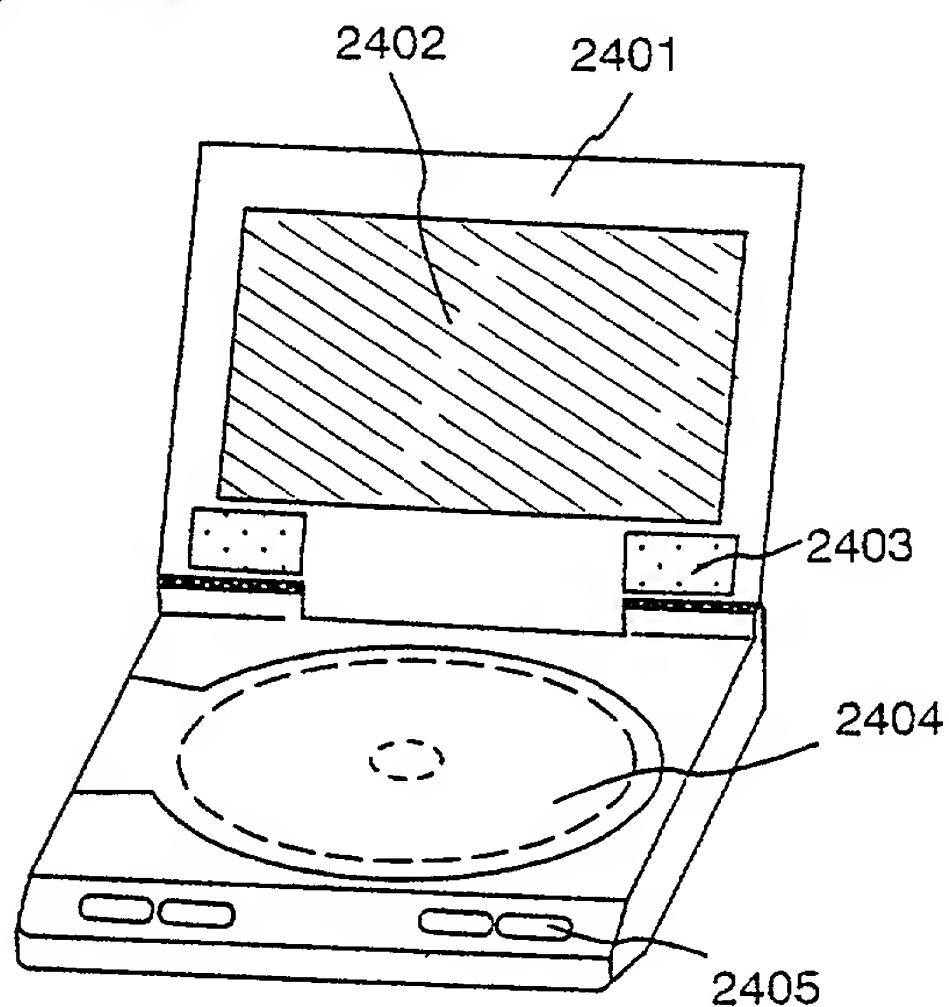


Fig. 20E

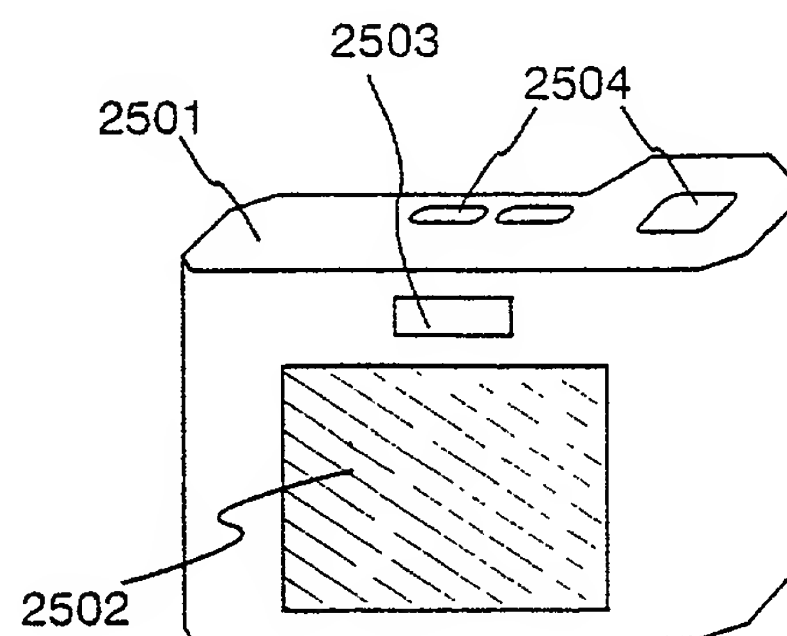


Fig. 20F

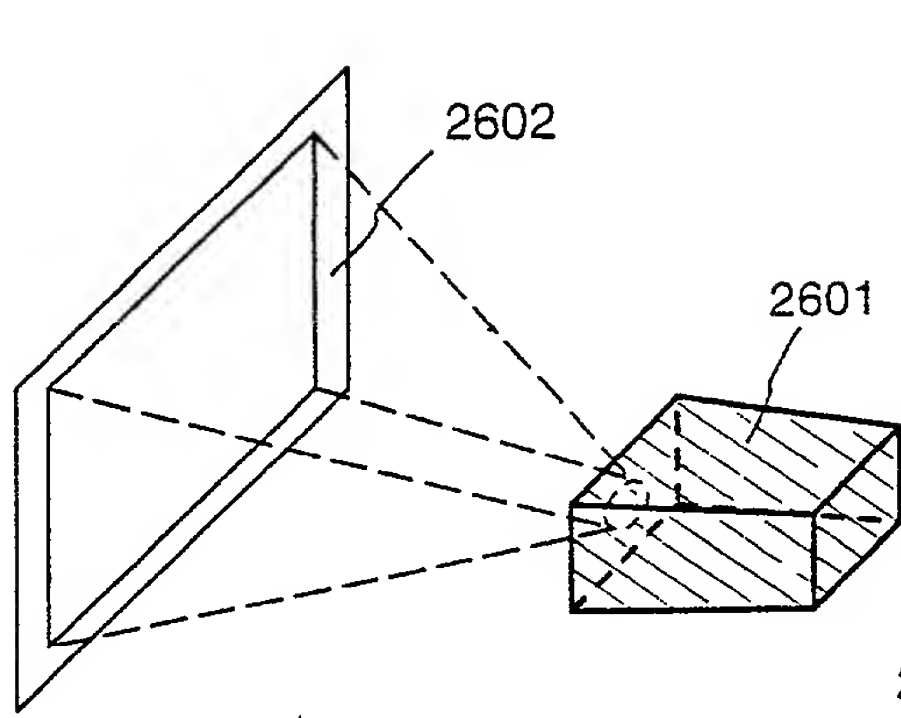


Fig. 21A

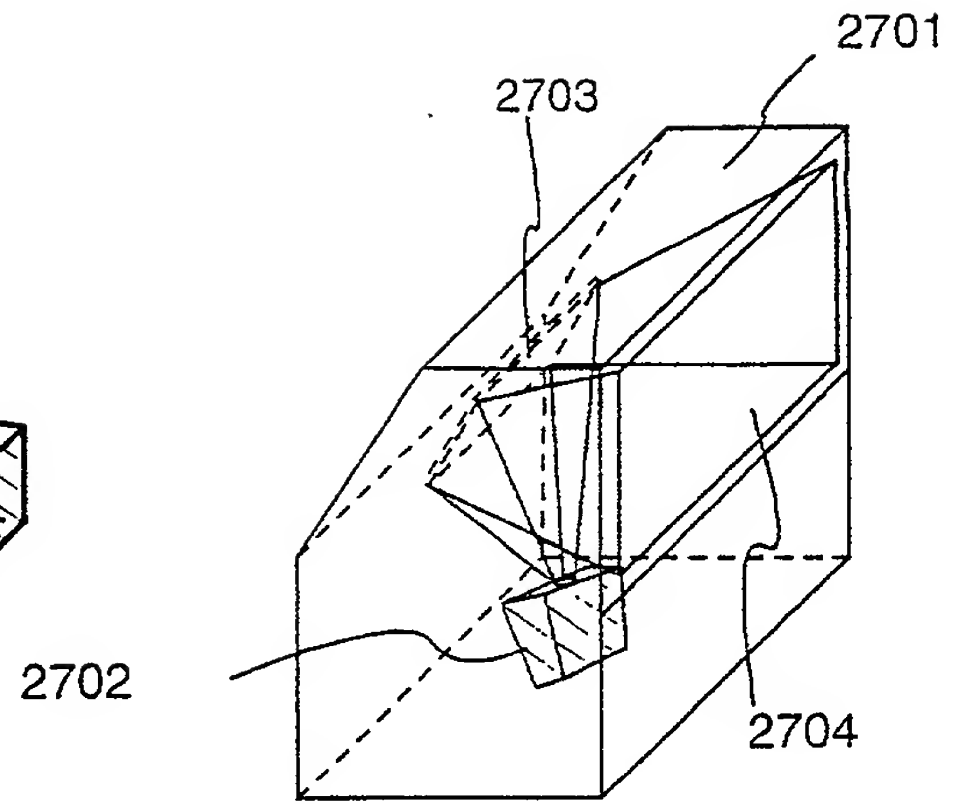


Fig. 21B

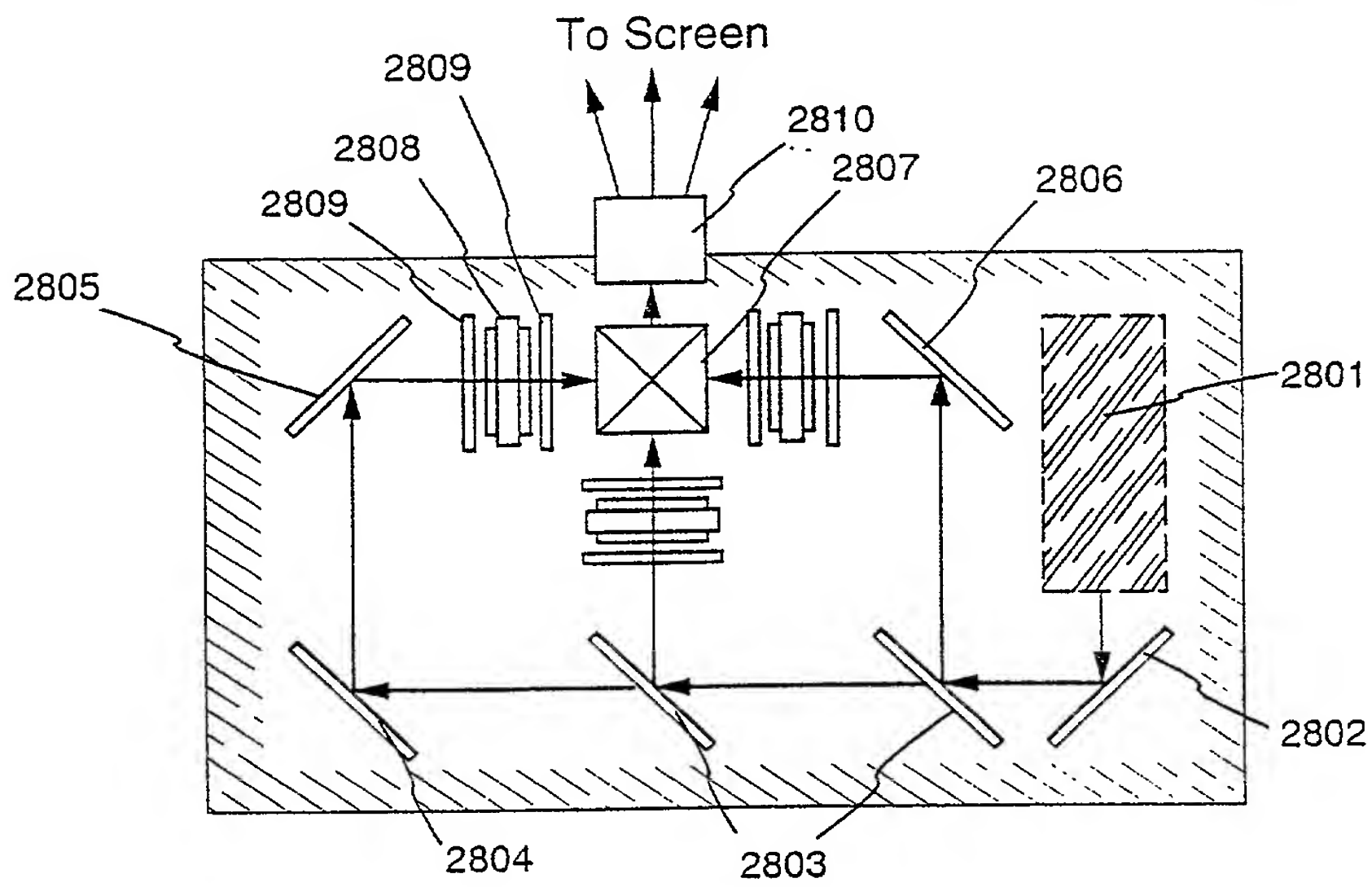


Fig. 21C

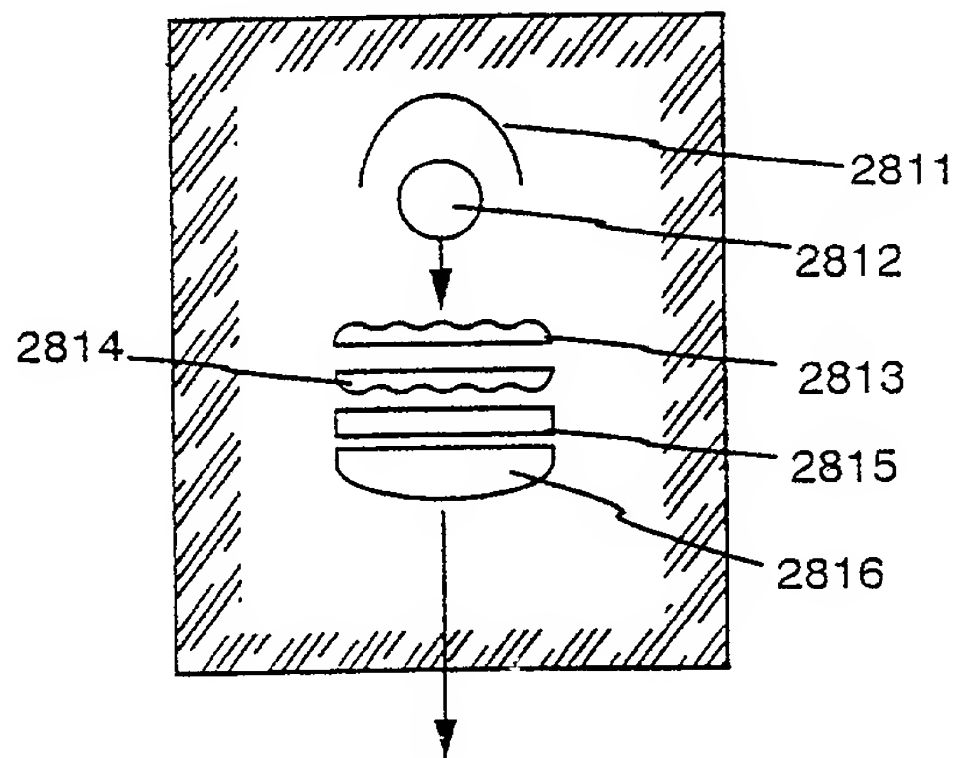


Fig. 21D

Fig. 22A

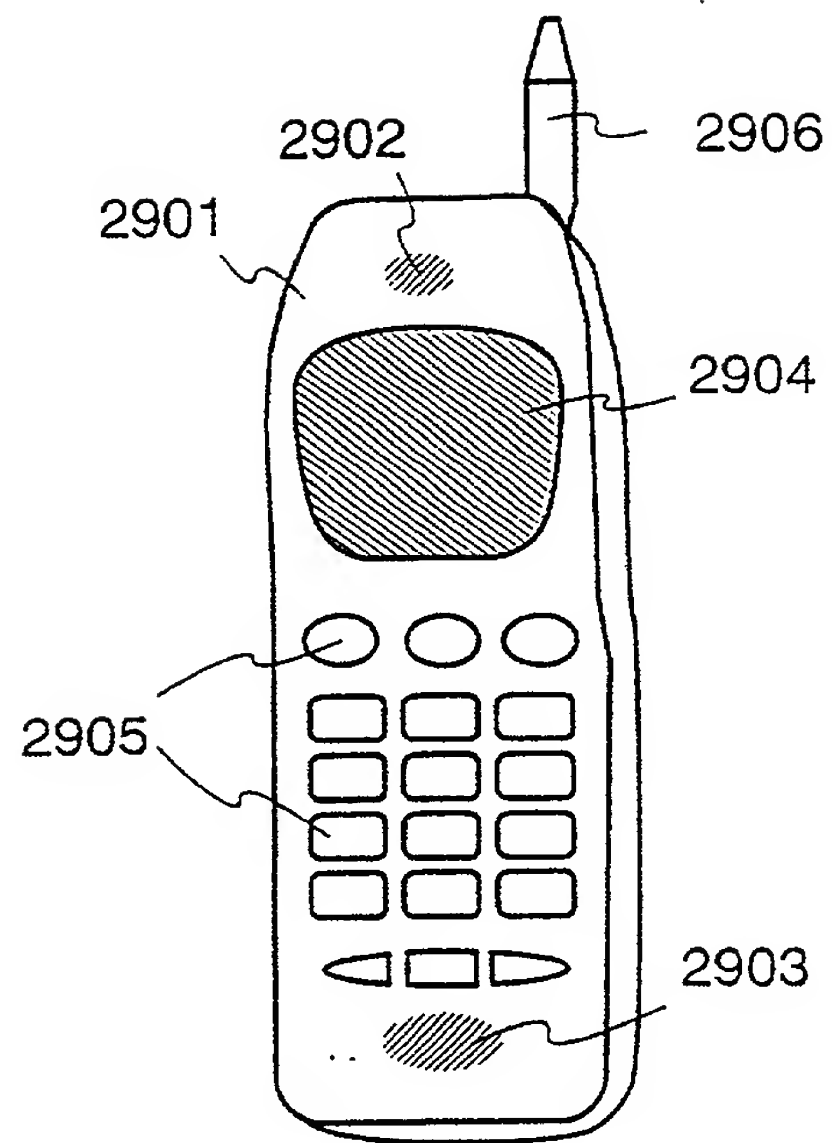


Fig. 22B

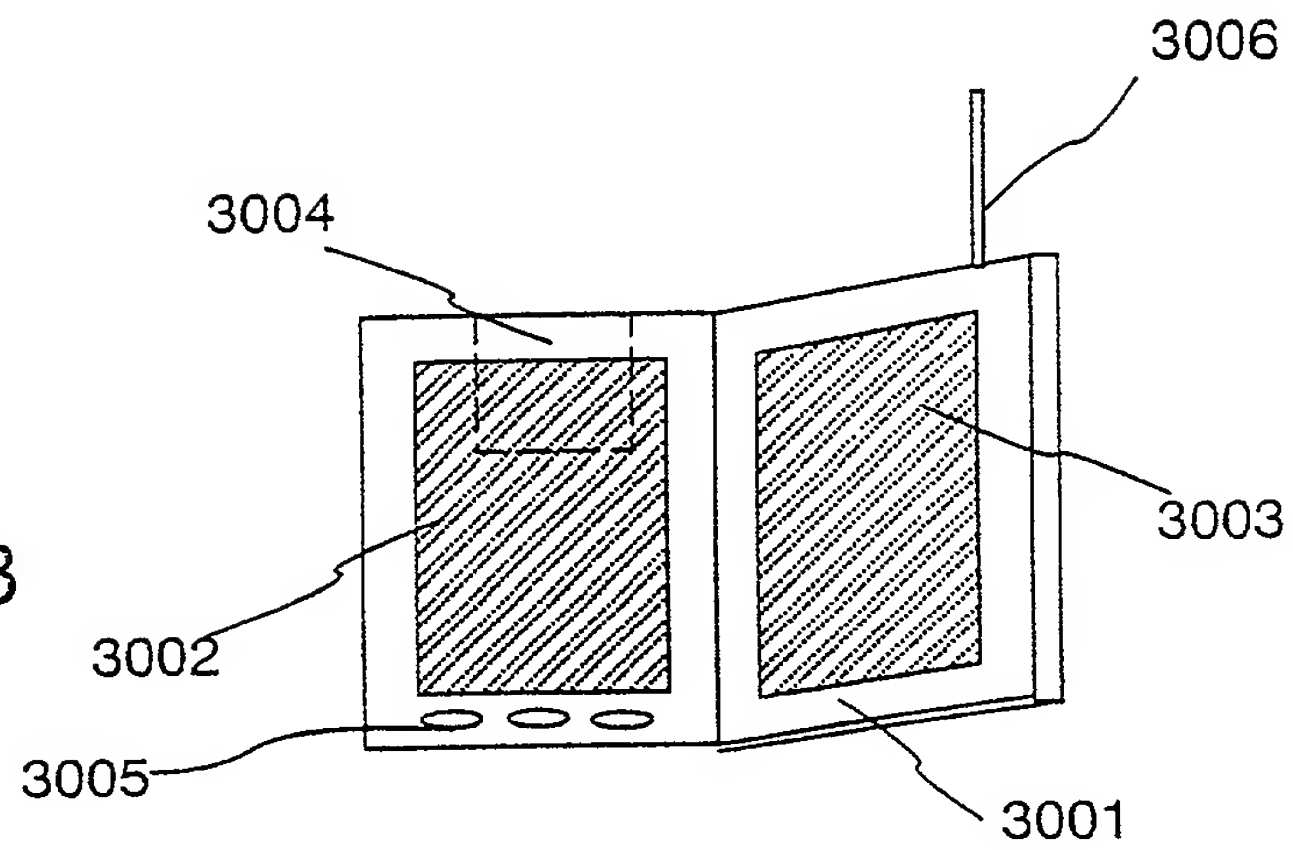
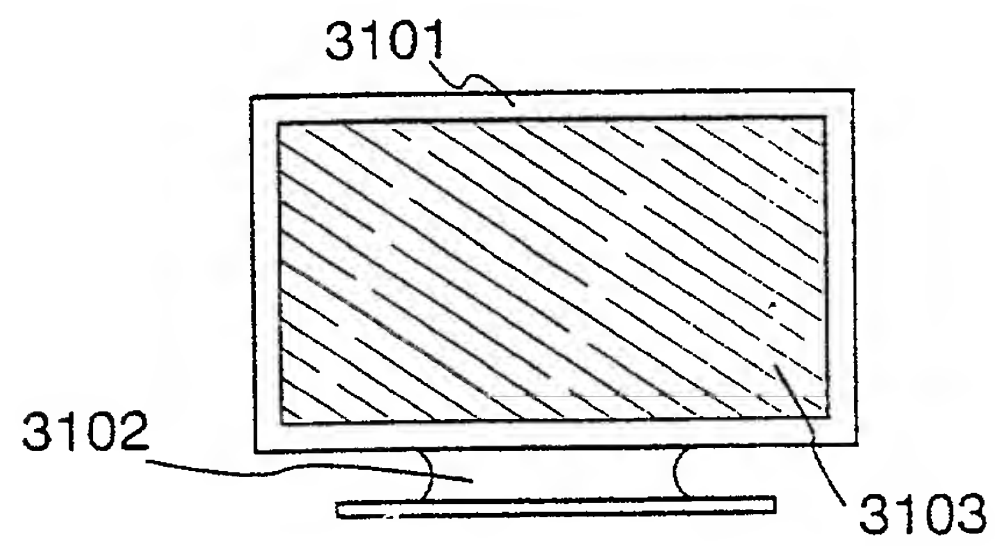


Fig. 22C



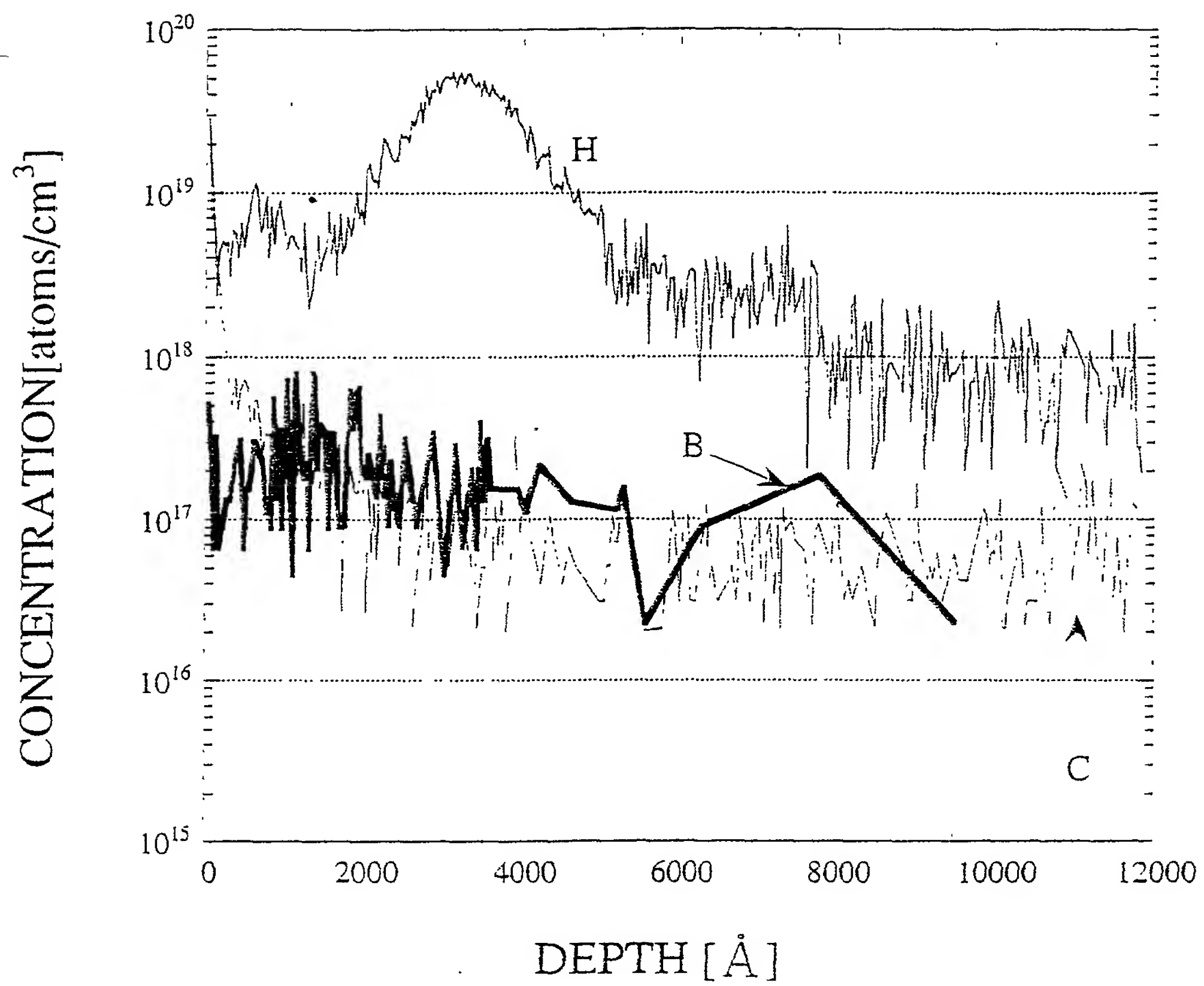


Fig. 23

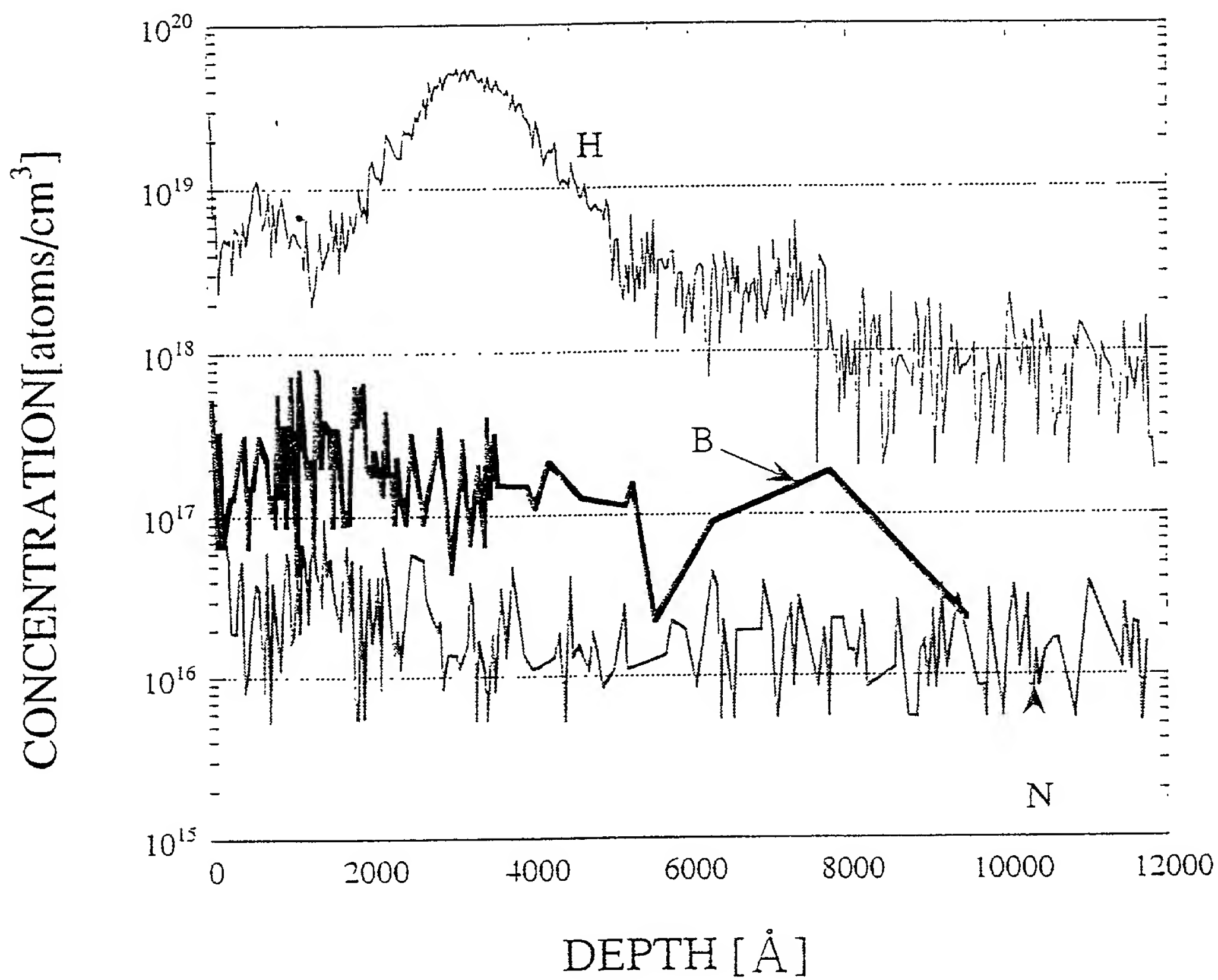


Fig. 24

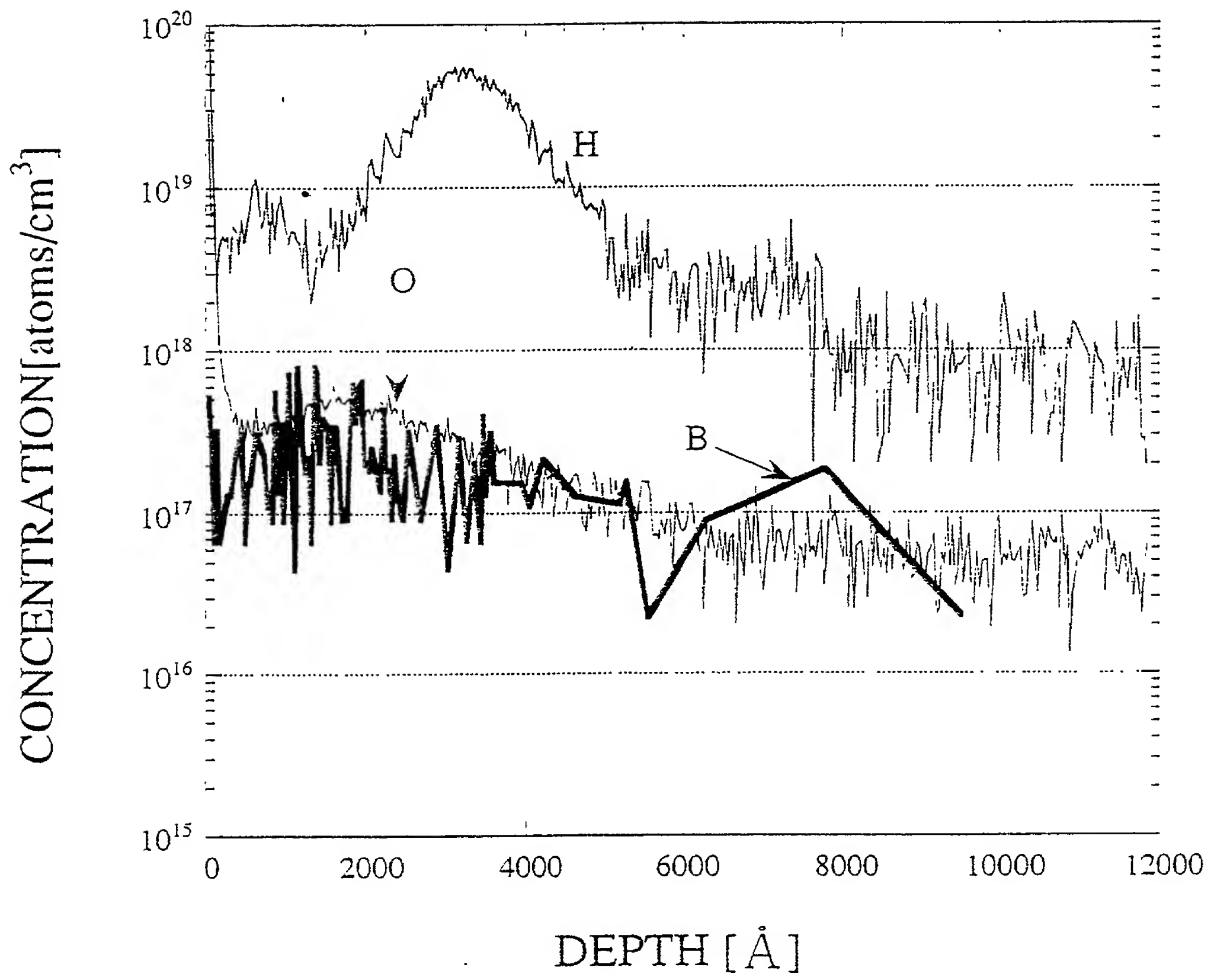


Fig. 25

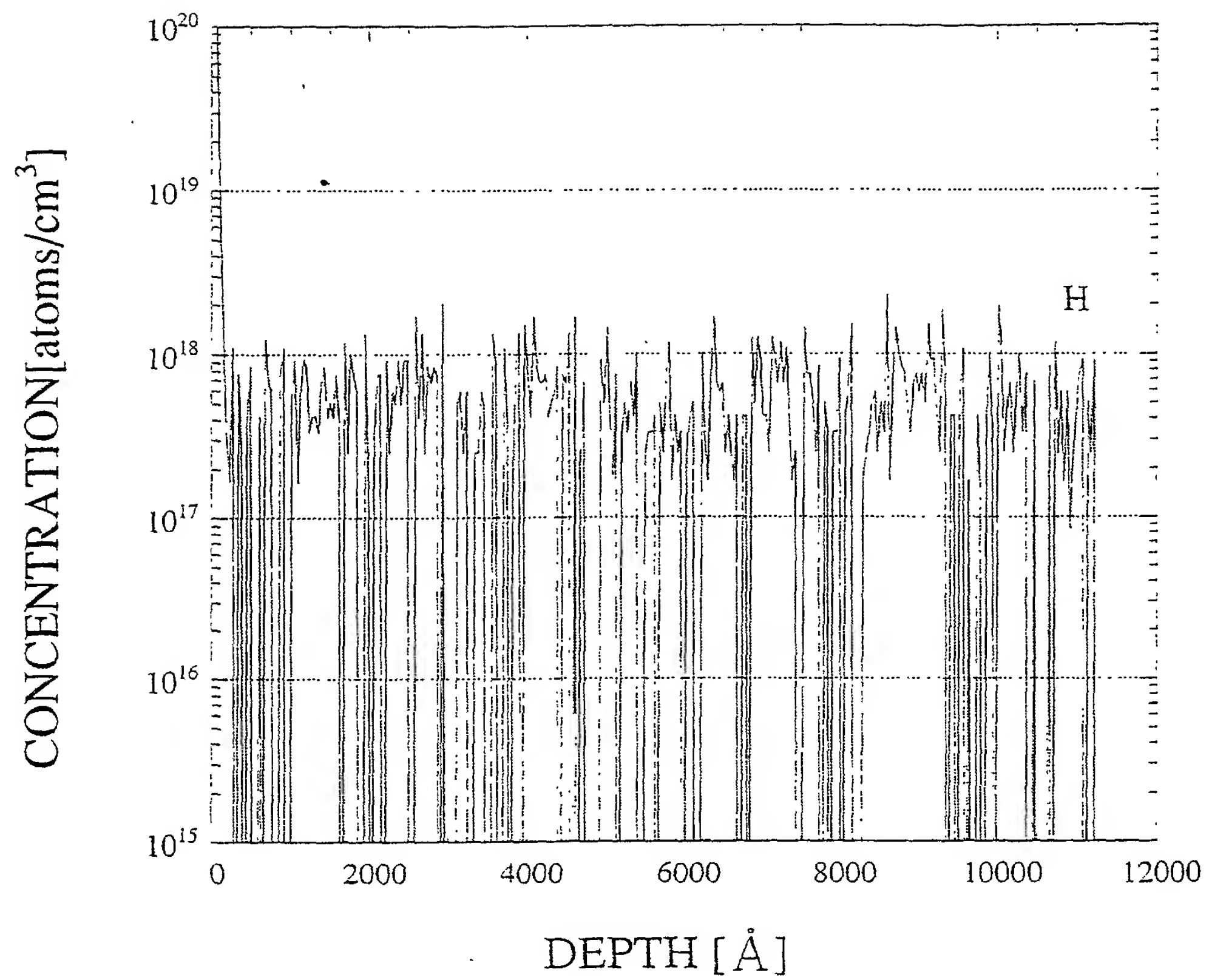


Fig. 26

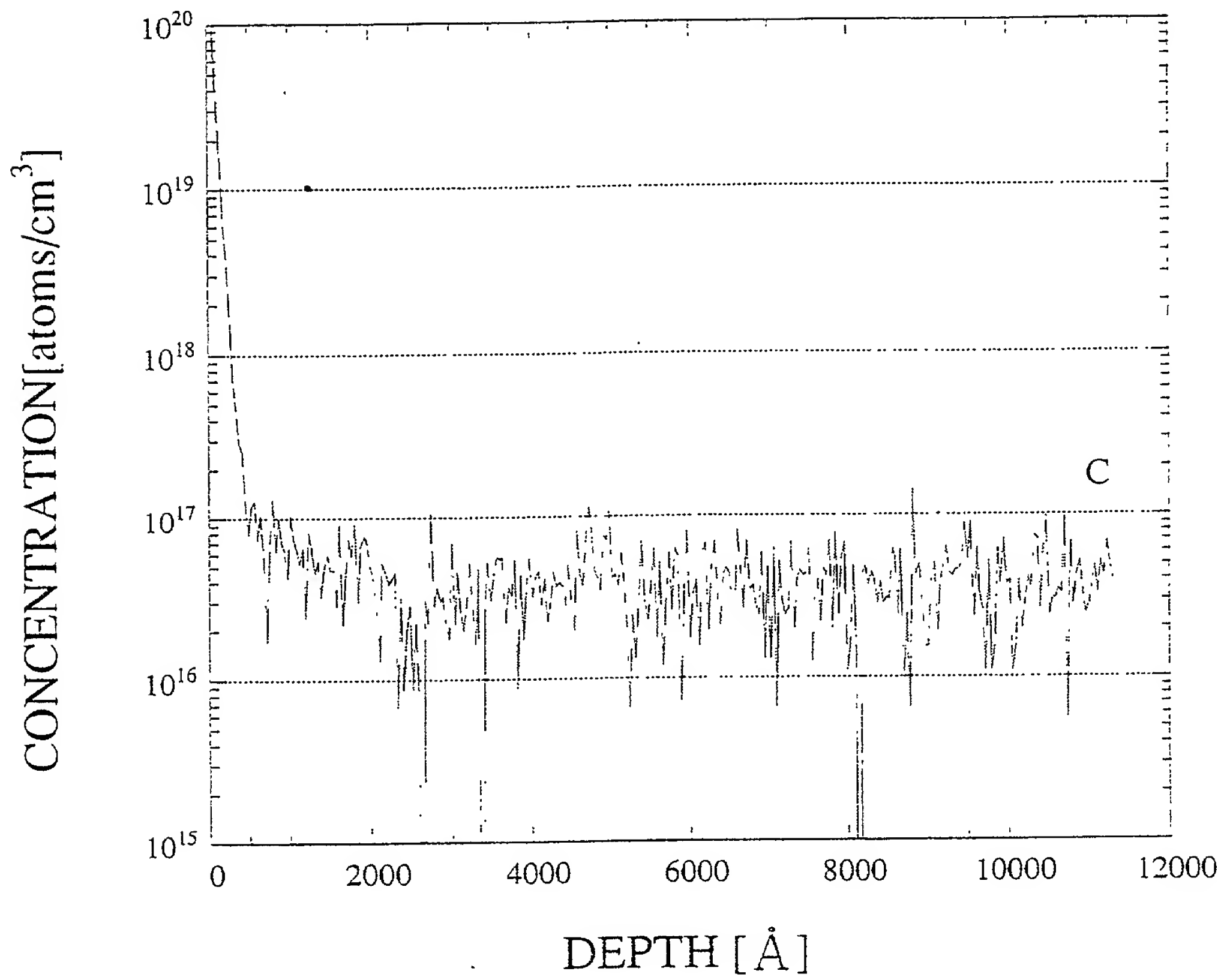


Fig. 27

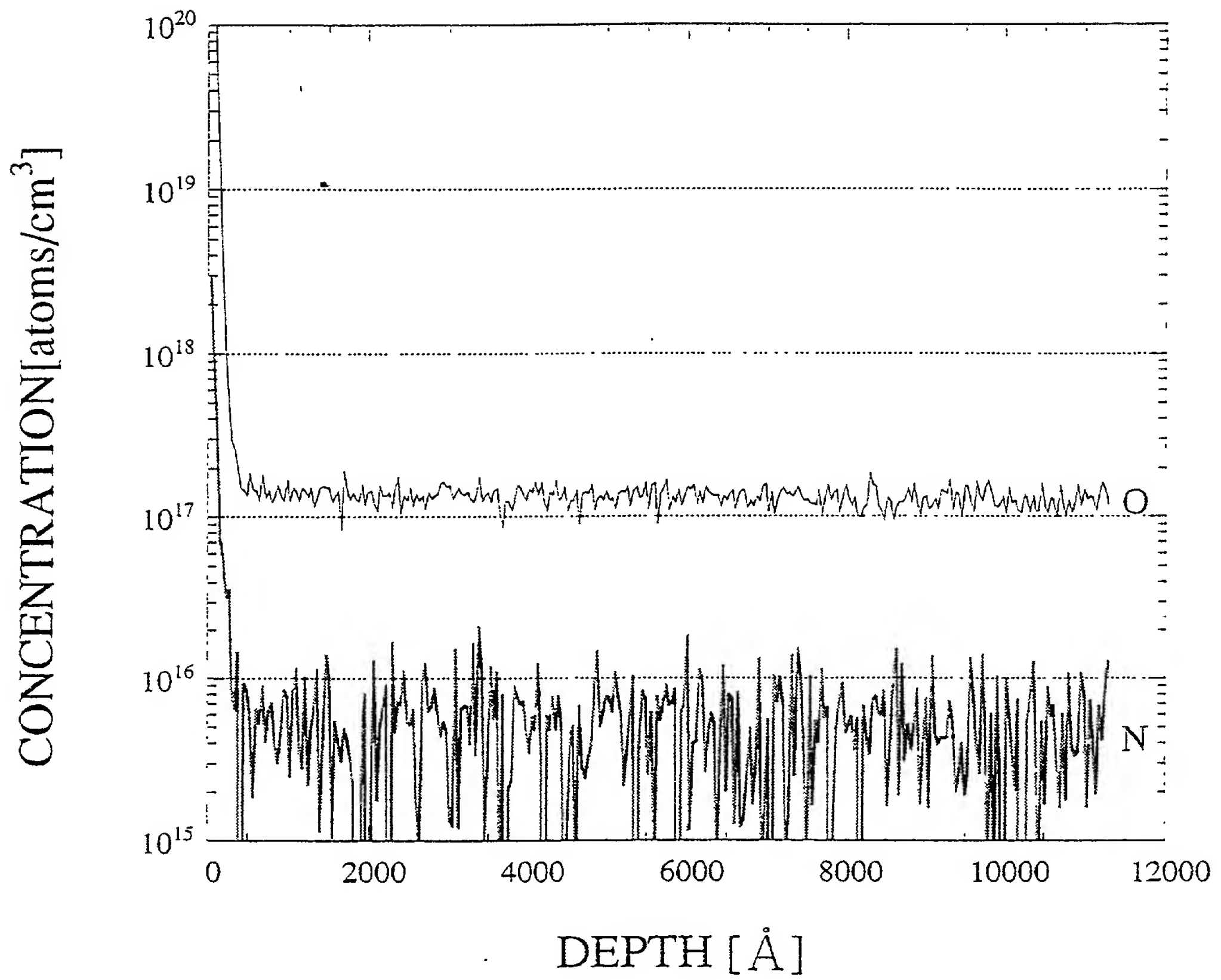
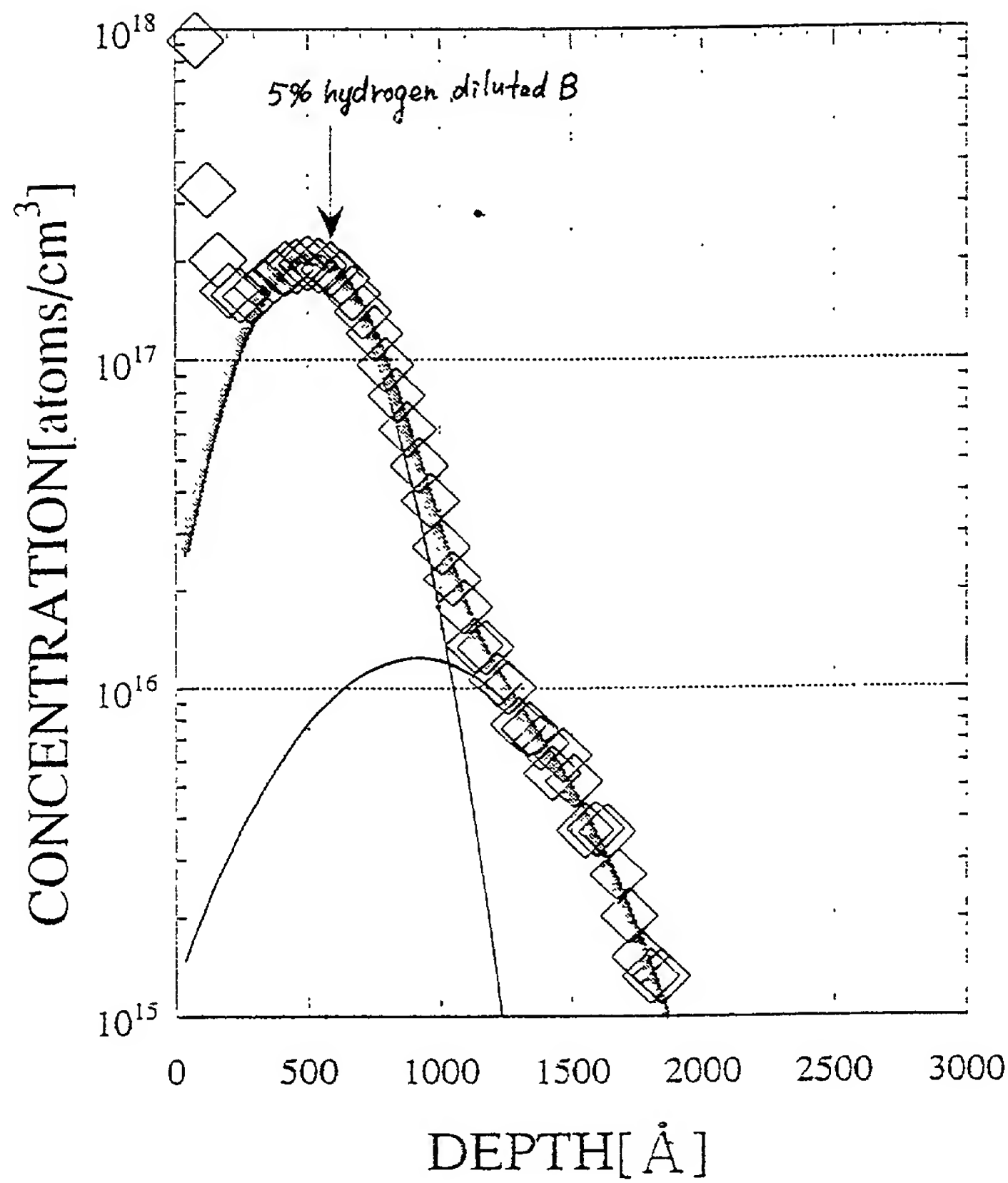


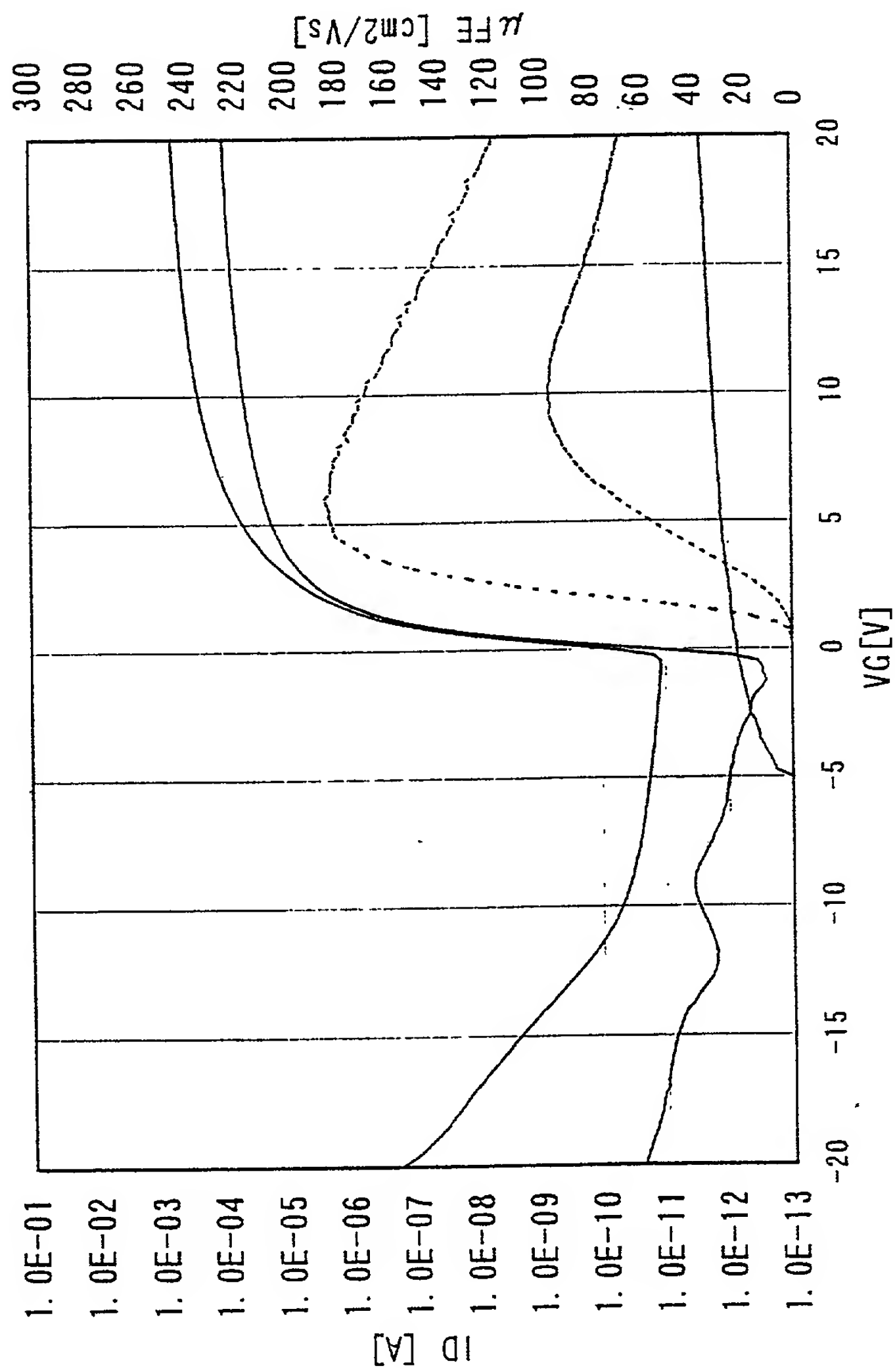
Fig. 28



5% B fitting	
	value
dosage 1	1.1224e+12
dosage 2	1.3183e+11
standard deviation 1	227.08
standard deviation 2	422.75
projected range 1	494.37
projected range 2	908.19
χ^2	0.52998
R	1

Gaussian function fitting
 projected range of B at 30kV (Å)
 LSS calculation (into Si or SiO₂)
 B⁺ : ~ 1000 Å
 B₂⁺ : ~ 500 Å

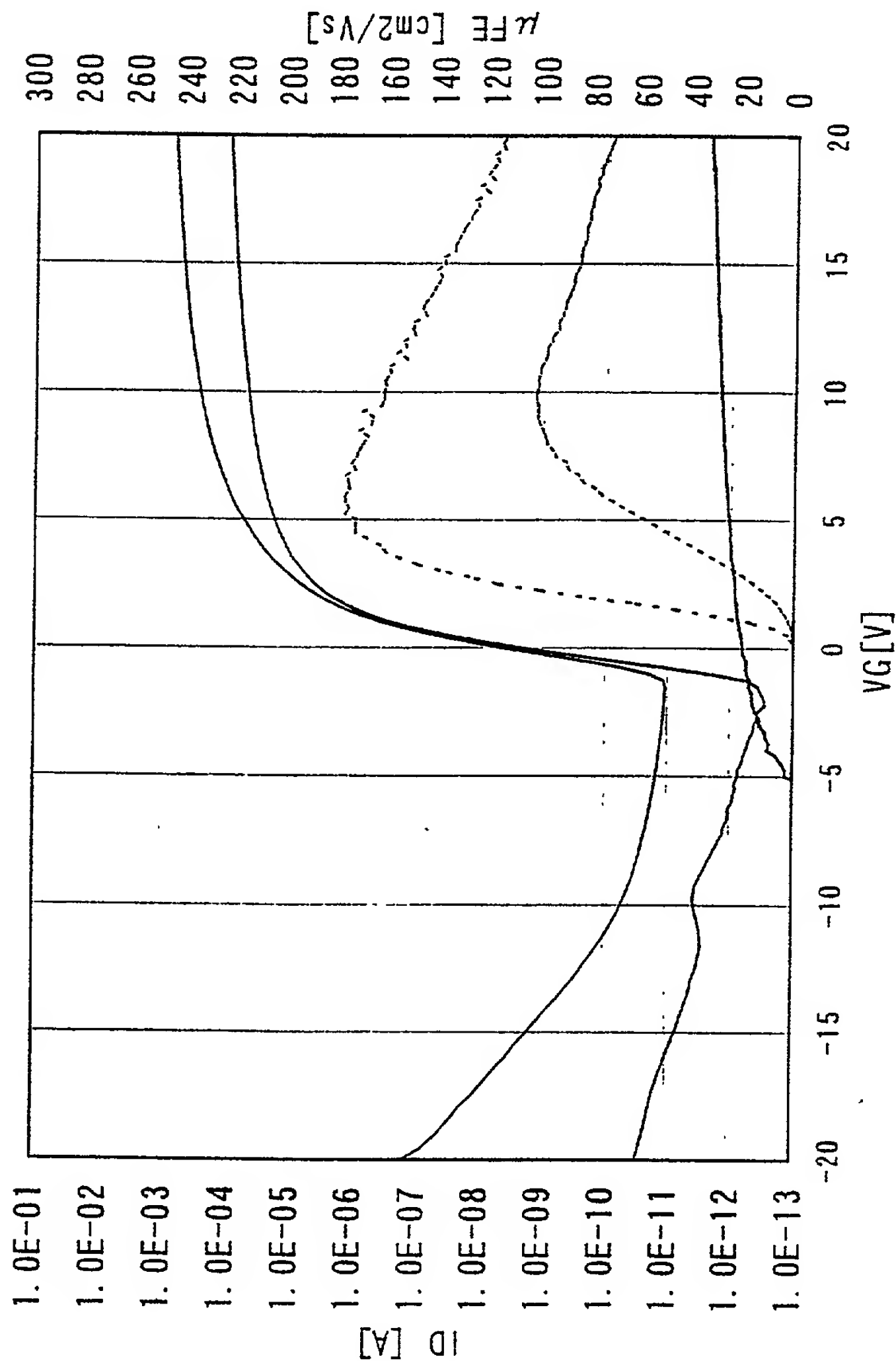
Fig. 29

[illegible]

parameter		
channel type		N
kind of TFT		A
value of L [μm]		7.1
value of W [μm]		7.5
dielectric constant		4.1
thickness of oxide film [\AA]		115
results		
$I_{\text{on_2}}$ [A]		$2.44\text{E-}04$
$I_{\text{off_2}}$ [A]		$1.70\text{E-}11$
Shift_1[V]		-0.231
V_{th} [V]		1.430
S-value [V/dec]		0.201
$\mu\text{FE}(\text{max})$ [cm^2/Vs]		185.2

Fig. 30

(N-ch, L/W= 7.1/ 7.5, Tox= 115)



parameters		
channel type		N
kind of TFT		A
value of L [um]		7.1
value of W [um]		7.5
dielectric constant		4.1
thickness of oxide film [nm]		115
results		
Ion_2	2.65E-04	
[A]		
Ioff_2	1.43E-11	
[A]		
Shift_1[V]	-1.086	
Vth	1.361	
[V]		
S-value	0.308	
[V/dec]		
$\mu_{FE}(\text{max})$	178.5	
[cm2/Vs]		

Fig. 31